Citations for Target : Si

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1951	Heller, Z. H. Tendam, D. J. **'The Stopping Power of Metals and Semiconductors'** ***Phys. Rev., 84, 905-09 (1951)*** *Comment : S. 9 MeV D -> Si, Ni, Cu, Ge, Zr, Rh, Ag, Sn, Air Rel. To Al*	**1951-Hell** 0067
1956	Gobeli, G. W. **'Range-Energy Relation for Low-Energy Alpha Particles in Si, Ge and Insb'** ***Phys. Rev., 103, 275-78 (1956)*** *Comment : R. 0.70-4.45 MeV He -> Si, Ge, InSb, Al, Cu, Ag, Au.*	**1956-Gobe** 0056
1958	Garin, A. Faraggi, H. **'Parcours Des Alpha De 4.5 MeV Dans L'Uranium, L'Or, Le Zirconium Et Le Silicium.'** ***J. Phys. Radium, 19, 76-78 (1958)*** *Comment : R. 4.5 MeV He -> Si, Zr, Au, U. Ranges From He-Particle Emission From Uranium Alloys.*	**1958-Gari** 0773
1962	Ewing, R. I. **'Response of Silicon Surface Barrier Detectors to Hydrogen Ions of Energies 25 to 250 keV'** ***IEEE Trans. Nucl. Sci., NS-09, No. 3, 207-10 (1962)*** *Comment : S. Rel. To H+. (70 keV/amu) H+2, H+3 -> Si*	**1962-Ewin** 0513
1963	Bilger, H. Baldinger, E. Czaja, W. **'Ionization von Si-Ruckstosskernen in Si-Zahldioden Bei Bestrahlung Mit Neutronen von 3. Bis 3.9 MeV.'** ***Helv. Phys. Acta, 36, 405-12 (1963)*** *Comment : S, Eta(Epsilon). 430 - 560 keV Si -> Si*	**1963-Bilg** 0245
1963	Primak, W. Dayal, Y. Edwards, E. **'Ion Bombardment of Silicon'** ***J. Appl. Phys., 34, 827-38 (1963)*** *Comment : R. 100 keV H -> Si*	**1963-Prim** 0570
1964	Davies, J. A. Ball, G. C. Brown, F. **'Crystallographic Dependence of Xe+ Penetration into Silicon at Low Energies'** ***Bull. Am. Phys. Soc., 9, 109b (1964)*** *Comment : R, dR. 20-80 keV Xe -> Si (Cryst.)*	**1964-Davi** 0169
1964	Davies, J. A. Ball, G. C. Brown, F. Domeij, B. **'Range of Energetic Xe125 Ions in Monocrystalline Silicon'** ***Can. J. Phys., 42, 1070-81 (1964)*** *Comment : R, dR. 5-80 keV 125Xe -> Si (Cryst.)*	**1964-Davi2** 0173
1964	Dearnaley, G. **'The Channeling of Ions through Silicon Detectors'** ***IEEE Trans. Nucl. Sci., NS-11, 249-53 (1964)*** *Comment : S, dS. 2 MeV H -> Si (Cryst.)*	**1964-Dear** 0171

1964
Erginsoy, C. Wegner, H. E. Gibson, W. M.
'Anisotropic Energy Loss of Light Particles of MeV Energies in Thin Silicon Single Crystals'
Phys. Rev. Letters, 13, 530-34 (1964)
Comment : S, dS. 2.8 MeV H -> Si (Cryst.)
1964-Ergi
0189

1964
Sattler, A. R. Silbert, M. G.
'Ionization of Energetic Silicon Atoms Within a Silicon Lattice'
Bull. Am. Phys. Soc., 9, 655-56 (1964)
Comment : S. 0.2-3.1 MeV Si -> Si
1964-Satt
0186

1965
Appleton, B. R. Erginsoy, C. Wegner, H. E. Gibson, W. M.
'Axial and Planar Effects in the Energy Loss of Protons in Silicon Single Crystals'
Phys. Letters, 19, 185-86 (1965)
Comment : S, dS. 4.85 MeV H -> Si (Cryst.)
1965-Appl
0224

1965
Brown, F. Ball, G. C. Channing, D. A. Howe, L. M. Pringle, J. P. S.
'Ranges of Heavy Ions'
Nucl. Inst. Methods, 38, 249-53 (1965)
Comment : R, dR. (20-150 keV) Na, K, Kr, Xe, Rb, Ce, Hg, Au -> Au, W, Si, Al, UO2 (Crystals)
1965-Brow
0613

1965
Grew, G. W.
'Cyclotron Tests to Determine the Response of Solid-State Detectors to Protons of Energies 50 to 160 MeV for Use in a Proton Spectrometer'
IEEE Trans. Nucl. Sci., NS-12, 308-13 (1965)
Comment : S,dS. 50-160 MeV H -> Si
1965-Grew
0515

1965
Sattler, A. R.
'Ionization Produced by Energetic Silicon Atoms Within a Silicon Lattice'
Phys. Rev. A, 138, 1815-21 (1965)
Comment : S. 21.2 - 3139 keV Si -> Si
1965-Satt
0216

1965
Wegner, H. E. Appleton, B. R. Erginsoy, C. Gibson, W. M.
'Axial and Planar Effects in the Energy Loss of Protons in Silicon Single Crystals'
Phys. Letters, 19, 187-89 (1965)
Comment : S,dS. 4.85 MeV H -> Si (Cryst.)
1965-Wegn
0595

1966
Appleton, B. R. Altman, M. Feldman, L. C. Gibson, W. M. Erginsoy, C.
'Least Energy Loss and Its Dispersion for þChanneledþ Protons in Silicon and Germanium Single Crystals'
Bull. Am. Phys. Soc., 11, 176 (1966)
Comment : S, dS. 3-11 MeV H -> Si, Ge (Both Cryst.)
1966-Appl
0257

1966
Bower, R. W. Baron, R. Mayer, J. W. Marsh, O. J.
'Deep (1-10 micrometer) Penetration of Ion-Implanted Donors in Silicon'
Appl. Phys. Letters, 9, 203-05 (1966)
Comment : R, dR. 20 keV Sb -> Si (Cryst.)
1966-Bowe
0301

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1966	Eisen, F. H. **'Channeling of 375 keV Protons through Silicon'** ***Phys. Letters, 23, 401-02 (1966)*** *Comment : S, dS. 375 keV H -> Si (Cryst.)*	**1966-Eise** 0275
1966	Gibbons, J. F. El-Hoshy, A. Manchester, K. E. Vogel, F. L. **'Implantation Profiles for 40 keV Phosphorous Ions in Silicon Single-Crystal Substrates'** ***Appl. Phys. Letters, 8, 46-48 (1966)*** *Comment : R, dR. 40 keV 32P -> Si (Cryst.)*	**1966-Gibb** 0243
1966	Lander, R. L. Mehlhop, W. A. Lubatti, H. J. Schnurmacher, G. L. **'Solid-State Devices as Detectors of High-Energy Interactions'** ***Nucl. Inst. Methods, 42, 261-68 (1966)*** *Comment : dS. 760 MeV H -> Si*	**1966-Land** 0423
1966	Maccabee, H. D. Raju, M. R. Tobias, C. A. **'Fluctuations of Energy Loss in Semiconductor Detectors'** ***IEEE Trans. Nucl. Sci., NS-13, No. 6, 176-79 (1966)*** *Comment : dS. 730 MeV H, 910 MeV He -> Si*	**1966-Macc** 0730
1967	DeCosnac, B. Dulien, P. Noel, J. P. **'Mesure De L'Energie Cedee Au Reseau Par Un Primaire Dans Le Silicium'** ***Rev. Physique Appl., 2, 158-63 (1967)*** *Comment : S, Eta(Epsilon). 100-400 keV Si -> Si*	**1967-DeCo** 0323
1967	Large, L. N. Hill, H. Ball, M. P. **'Profiles of High Conductivity Shallow Layers in Silicon Produced by Boron Ion Implantations'** ***Int. J. Elec., 22, 153-64 (1967)*** *Comment : R, dR. 25-125 keV B -> Si*	**1967-Larg** 0649
1967	Marcinkowski, A. Rzewuski, H. Werner, Z. **'Range-Energy Relation for Low Energy Protons in Si and Ge'** ***Nucl. Inst. Methods, 57, 338-40 (1967)*** *Comment : R. 0.8 - 1.9 MeV H -> Ge, Si.*	**1967-Marc** 0312
1967	Remillieux, J. Samueli, J. J. Sarazin, A. **'Etude Des Effets Directionnels Dans La Transmission De Protons De 2 MeV a Travers Un Monocristal De Silicium'** ***J. Physique, 28, 832-38 (1967)*** *Comment : S, dS. 2 MeV H -> Si (Cryst.)*	**1967-Remi** 0602
1968	Bulthuis, K. **'Anomalous Penetration of Ga and in Implanted in Silicon'** ***Phys. Letters A, 27, 193-94 (1968)*** *Comment : R, dR. 56 keV In, Ga -> Si (Cryst.)*	**1968-Bult** 0348

1968 Davies, D. E. **1968-Davi** 0376
'Range and Distribution of Implanted Boron in Silicon'
Appl. Phys. Letters, 13, 243-45 (1968)
Comment : R, dR. 200-400 keV B -> Si

1968 Dearnaley, G. Freeman, J. H. Gard, G. A. Williams, M. A. **1968-Dear** 0334
'Implantation Profiles of 32P Channeled into Silicon Crystals'
Can. J. Phys., 46, 587-95 (1968)
Comment : R, dR. 10-110 keV 32P -> Si (Cryst.)

1968 Eisen, F. H. **1968-Eise** 0339
'Channeling of Medium-Mass Ions through Silicon'
Can. J. Phys., 46, 561-72 (1968)
Comment : S. 100-500 keV B, C, N, O, F, Ne, Na, Mg, Al, Si, P, Cl, Ar, K -> Si (Cryst.)

1968 Kleinfelder, W. J. Johnson, W. S. Gibbons, J. F. **1968-Klei** 0333
'Impurity Distribution Profiles in Ion-Implanted Silicon'
Can. J. Phys., 46, 597-606 (1968)
Comment : R, dR. 10-70 keV B, N, P, As -> Si (Cryst.)

1968 Kolats, J. J. Amos, T. M. Bichsel, H. **1968-Kola** 0372
'Energy-Loss Straggling of Protons in Silicon'
Phys. Rev., 176, 484-89 (1968)
Comment : dS. 5-42 MeV H -> Si

1968 Maccabee, H. D. Raju, M. R. Tobias, C. H. **1968-Macc** 0314
'Fluctuations of Energy Loss by Heavy Charged Particles in Thin Absorbers'
Phys. Rev., 165, 469-74 (1968)
Comment : dS. 45, 730 MeV H, 910 MeV He, 370 MeV Pi- -> Si

1968 Manchester, K. E. **1968-Manc** 0603
'Radiotracer Study of Ion Implanted Profile Build-Up in Silicon Substrates'
J. Electrochem. Soc., 115, 656-59 (1968)
Comment : R, dR. 40 keV 31P, 32P -> Si (Cryst.)

1968 Mannami, M. Fujimoto, F. Ozawa, K. **1968-Mann** 0320
'Anomalous Energy Losses of 1.5 MeV Protons Channeled in Silicon Single Crystals.'
Phys. Letters A, 26, 201-02 (1968)
Comment : S, dS. 1.5 MeV H -> Si (Cryst.)

1968 Roosild, S. Dolan, R. Buchanan, B. **1968-Roos** 0650
'Semiconductor Doping by High Energy 1 - 2.5 MeV Ion Implantation.'
J. Electrochem. Soc., 115, 307-11 (1968)
Comment : R, dR. 1-2.5 MeV B, 1-1.6 MeV N, 1 MeV P -> Si. Electrical Junction Measurements.

1968
Sattler, A. R.   Dearnaley, G.
'Channeling in Diamond-Type and Zinc-Blende Lattices: Comparative Effects in Channeling of Protons and Deuterons in Ge, GaAs, and Si'
Phys. Rev., 161, 244-52 (1967)(Erratum, Phys. Rev., 165, 750 (1968))
Comment : *S. 4-7.6 MeV H, D -> Ge, GaAs, Si (All Cryst.)*
1968-Satt
0308

1968
Schwuttke, G. H.   Brack, K.   Gardner, E. E.   DeAngelis, H. M.
'High Energy Nitrogen Doping of Single-Crystal Silicon'
"Radiation Effects in Semiconductors", Plenum Press, NY, 406-417 (1968)
Comment : *R. N (2 MeV) -> Si One of the earliest MeV implantation papers.*
1968-Schw
2132

1968
Shipatov, E. T.   Kononov, B. A.
'Investigation of the Channeling of Protons in Single Crystals of Ionic Compounds and Semiconductors'
Izv. Vuz. Fiz. No. 9, 52-56 (1968). [Engl. Trans. Soviet Phys. J. No. 9, 46-49, (1968)]
Comment : *S,dS. H (4.7-6.7 MeV) -> NaCl, KCl, KBr, Si, Ge (crystals)*
1968-Ship2
0599

1968
Shipatov, E. T.   Kononov, B. A.
'Energy Distribution of 6.72 MeV Protons Passing through Monocrystals.'
Atomnaya Energiya (USSR), 25, 439-40 (1968) [Engl. Trans. Sov. Atom. Energy, 25, 1254-55 (1968).
Comment : *S, dS. 6.72 MeV H -> NaCl, KCl, KBr, Si, Ge (All Cryst.)*
1968-Ship3
0653

1968
Stephen, J.   Smith, B. J.   Hinder, G. W.   Marshall, D. C.   Wittam, E. M.
'Some Observations of High Energy Nitrogen Implantations in Silicon'
"Radiation Effects in Semiconductors", Plenum Press, NY, 489-494 (1968)
Comment : *R. N (3 MeV) -> Si One of the earliest MeV implantation papers.*
1968-Step
2133

1968
Tschalar, C.   Bichsel, H.
'Mean Excitation Potential of Light Compounds'
Phys. Rev., 175, 476-8 (1968)
Comment : *R. 3-30 MeV H -> Si, Al, SiO2, Al2O3, C3H5O2*
1968-Tsch3
0904

1968
Zorin, E. I.   Pavlov, P. V.   Tetelbaum, D. I.
'Investigation of Boron Atom Distribution in Silicon Doped by Ion Bombardment Method'
Fiz. Tverd. Tela, 9, 3642-44 (1967). [Engl. Trans. Sov. Phys. Solid State, 9,2874-76 (1968).
Comment : *R, dR. 20-60 keV B -> Si*
1968-Zori
0656

1969
Aitken, D. W.   Lakin, W. L.   Zulliger, H. R.
'Energy Loss and Straggling in Silicon by High-Energy Electrons, Positive Pions, and Protons'
Phys. Rev., 179, 393-98 (1969)
Comment : *S, dS. 29-300 MeV H, 50-200 MeV Pi+ -> Si*
1969-Aitk
0385

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1969	Arkhipov, E. P. Gott, Yu. V. **'Slowing Down of 0.5 - 30 keV Protons in Some Materials.'** ***Zh. Eksp. Teor. Fiz., 56, 1146-51 (1969). [Engl. Trans. Sov. Phys. Jetp, 29, 615-18 (1969)*** *Comment : S. 0.5-30 keV H -> C, Ti, Al, Cu, Ni, Fe, Ge, Si, Sb, Bi*	**1969-Arkh** 0410
1969	Clark, G. J. Dearnaley, G. Morgan, D. V. Poate, J. M. **'The Stopping Power of Protons Channelled through Csi Crystals'** ***Phys. Letters A, 30, 11-12 (1969)*** *Comment : S. 4 MeV H -> Si (Cryst.)*	**1969-Clar** 0127
1969	Davies, D. E. **'Range of Implanted Boron, Phosphorus, and Arsenic in Silicon'** ***Can. J. Phys., 47, 1750-53 (1969)*** *Comment : R, dR. 0.15-1.8 MeV B, 1.0-1.7 MeV As, 0.5-1.7 MeV P -> Si*	**1969-Davi** 0380
1969	Fairfield, J. M. Crowder, B. L. **'Ion Implantation Doping of Silicon for Shallow Junctions'** ***Trans. Met. Soc. Aime, 245, 469-473 (1969)*** *Comment : R,dR. 70-280 keV B, P, 80-480 keV As -> Si*	**1969-Fair** 0552
1969	Schwuttke, G. H. Brack, K. **'Annealing of High Energy Ion Implantation Damage in Single Crystal Silicon'** ***Trans. Metal. Soc. (AIME), 245, 475-481 (1969)*** *Comment : R. N (1.5-2.0 MeV) -> Si One of the earliest MeV implantation papers.*	**1969-Schw** 2135
1969	Shipatov, E. T. **'Energy and Angular Distributions of Protons Transmitted by Germanium and Silicon Single Crystals Along (110) and (100) Channels in the Crystal Lattice'** ***Fiz. Tekh. Poluprovodnikov, 2, 1690-91 (1968). [Engl. Trans. Sov. Phys. Semicond., 2, 1408-09 (1969)*** *Comment : S, dS. 6.72 MeV H -> Si, Ge (Both Cryst.)*	**1969-Ship2** 0654
1970	Apel, D. Muller-Jahreis, U. Schwabe, S. **'On the Z2-Dependence of Electronic Stopping Cross Section'** ***Phys. Stat. Sol. A, 3, K173-75 (1970)*** *Comment : S. 10-100 keV Li -> Si, V, Cr, Fe, Ge, Se*	**1970-Apel** 0655
1970	Avdeichikov, V. V. Gridnev, G. F. Lozhkin, O. V. Perfilov, N. A. **'The Limiting Energy Resolution of Thin De/Dx Detectors for 5-9 MeV Alpha Particles'** ***Bull. Acad. Sci. USSR Phys. Ser., 34, No. 1, 190-96 (1970)*** *Comment : dS. 5-8.7 MeV He -> Si*	**1970-Avde** 0711

1970
Bader, R. Kalbitzer, S.
'Low Energy Boron and Phosphorus Implants in Silicon. (B). Doping Profiles.'
Rad. Effects, 6, 211-16 (1970)
Comment : R, dR. 6 keV B, 15 keV P -> Si (Cryst.).
1970-Bade
0831

1970
Cairns, J. A. Holloway, D. F. Nelson, R. S.
'Measurement of Implanted Boron Concentration Profiles in Silicon by the Use of Heavy Ion X-Ray Excitation'
Proc. of the European Conference on Ion Implantation. Peter Peregrinus, Publisher, Stevenhage, England, P. 203-06 (1970)
Comment : R, dR. 40, 100 keV B -> Si
1970-Cair
0695

1970
Cairns, J. A. Nelson, R. S. Briggs, J. S.
'The Use of the Ion-Induced X-Rays to Investigate the Concentration Distribution and Atom Location of Boron-Implanted Silicon, in I'
Ruge and J. Graul (Ed.): Ion Implantation in Semiconductors. Springer, Berlin, P. 299-306 (1970)
Comment : R. 100-300 keV B -> Si
1970-Cair2
0617

1970
Crowder, B. L.
'The Role of Damage in the Annealing Characteristics of Ion Implanted Si'
J. Electrochem. Soc., 117, 671-74 (1970)
Comment : R, dR. 280 keV 31P -> Si
1970-Crow
0644

1970
Davies, D. E.
'The Implanted Profiles of Boron, Phosphorus, and Arsenic in Silicon from Junction Depth Measurements'
Solid-State Elec., 13, 229-237 (1970)
Comment : R. 0.1-2.0 MeV B, P, As -> Si
1970-Davi
1006

1970
Davies, D. E. Roosild, S. A.
'Minority Carrier Lifetime in Ion Implanted and Annealed Silicon'
Appl. Phys. Letters, 17, 107-109 (1970)
Comment : R. C (1-2 MeV) -> Si
1970-Davi2
2136

1970
Dearnaley, G. Wilkens, M. A. Goode, P. D. Freeman, J. H. Gard, G. A.
'The Range Distribution of Radioactive Ions Implanted into Silicon Crystals'
W. Palmer, M. W. Thompson, P. D. Townsend: Atomic Collision Phenomena in Solids. North-Holland, Amsterdam, P. 623-55 (1970)
Comment : R, dR. 40-120 keV P, Na, S, Cu, Kr -> Si, Cryst. and Amorph.
1970-Dear2
0027

1970
Feldman, L. C. Rodgers, J. W.
'Depth Profiles of the Lattice Disorder Resulting from Ion Bombardment of Silicon Single Crystals'
J. Appl. Phys., 41, 3776-3782 (1970)
Comment : R. 200-500 keV C, Ne -> Si
1970-Feld
0972

1970
Gamo, K. Masuda, K. Namba, S. Ishihara, S. Itsuro, K.
1970-Gamo
0971
'Enhanced Diffusion of High-Temperature Ion-Implanted Antimony into Silicon'
Appl. Phys. Letters, 17, 391-393 (1970)
Comment : *R. 20 keV Sb -> Si*

1970
Kononov, B. A. Struts, V. K.
1970-Kono
0646
'Channeling of Protons in Silicon at Different Temperatures'
Izv. Vuz. Fiz. No. 6, 60-63 (1970). [Engl. Trans. Sov. Phys. J., 13, 738-61 (1970)]
Comment : *S, dS. 6.72 MeV H -> Si (Cryst.)*

1970
Lecrosnier, D. P. Pelous, G. P.
1970-Lecr
0698
'High Energy Boron Implantation into Silicon'
Proc. of the European Conference on Ion Implantation. Peter Peregrinus, Publisher, Stevenhage, England, P. 106-06 (1970)
Comment : *R, dR. 1-2.5 MeV 11B -> Si*

1970
Meyer, O. Mayer, J. W.
1970-Meye
0648
'Analysis of Rb and Cs Implantations in Silicon by Channeling and Hall Effect Measurements'
Solid-State Elec., 13, 1357-1362 (1970)
Comment : *R, dR. 5-50 keV Rb, Cs -> Si*

1970
Nelson, R. S. Cairns, J. A.
1970-Nels
0659
'Antimony Implanted Silicon: a Comparison Between the Total Implanted Concentration Profile and the Donor Concentration Profile'
Rad. Effects, 6, 131-34 (1970)
Comment : *R, dR. 100 keV Sb -> Si*

1970
Pistryak, V. M. Gnap, A. K. Kozlov, V. F. Garber, R. I. Fedorenko, A. I.
1970-Pist
0721
'Concentration Profile of Boron Ions Implanted into Silicon with Energies of 30 and 100 keV'
Fiz. Tverd. Tela, 12, 1281-82 (1970). [Engl. Trans. Sov. Phys. Solid State, 12, 1005-06 (1970).
Comment : *R, dR. 30, 100 keV B -> Si (Cryst.)*

1970
Schwuttke, G. H.
1970-Schw
2124
'Crystal Properties as Influenced by Crystallographic Imperfections: High Energy Ion Implantation'
United States Air Force: AFCRL-70-0459 (1970)
Comment : *R, dR. C, N, O (1.0-2.0 MeV) -> Si One of the earliest studies of MeV implantation into silicon.*

1970
Stein, H. J. Vook, F. L. Borders, J. A.
1970-Stei
0969
'Depth Distribution of Divacancies in 400-keV O+ Ion-Implanted Silicon'
Appl. Phys. Letters, 16, 106-108 (1970)
Comment : *R. 400 keV O -> Si*

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1970	Stumpfi, W. Kalbitzer, S. **'Low Energy Boron and Phosphorus Implants in Silicon (a) Electrical Sheet Measurements'** ***Rad. Effects, 6, 205-210 (1970)*** *Comment : R,dR. B, P (7 keV) -> Si*	**1970-Stum** 2005
1971	Chemin, J. F. Roturier, J. Petit, G. Y. **'Mesure par Reactions Nucleaires Resonnantes du Relentissement et de la Dispersion en Energie de Protons'** ***J. Phys. (Paris), 32, 220 (1971)*** *Comment : S,dS. H (1-4 MeV) -> Si.*	**1971-Chem** 1634
1971	Crowder, B. L. **'The Influence of the Amorphous Phase on Ion Distributions and Annealing Behavior of Group Iii and Group V Ions Implanted into Silicon'** ***J. Electrochem. Soc., 118, 943-52 (1971)*** *Comment : R,dR. (50-300 keV) B, Al Ga, P, As, Sb, Bi -> Si*	**1971-Crow** 0454
1971	Daview, D. E. Roosild, S. **'Residual Electrically Active Defects after Lattice Reordering in Ion Implanted Silicon'** ***Appl. Phys. Letters, 18, 548-550 (1971)*** *Comment : R. C (2 MeV) -> Si*	**1971-Davi** 2137
1971	Dearnaley, M. A. Wilkins, M. A. Goode, P. D. **'Non-Gaussian Implantation Profiles'** ***Intl. Conf. Ion Implantation in Semiconductors, Ed. by I. Ruge and J. Graul, 439-454 (1971)*** *Comment : R. 40-120 keV S, P ->Si*	**1971-Dear** 1010
1971	DellaMea, G. Drigo, A. V. LoRusso, S. Mazzoldi, P. Bentini, G. G. **'Energy Loss of H, D, and 4He Ions Channeled through Thin Single Crystals of Silicon'** ***Phys. Rev. Letters, 27, 1194-96 (1971)*** *Comment : S. 0.9-5.0 MeV H, D, He -> Si Cryst. And Amorph.*	**1971-Dell** 0132
1971	Gamo, K. Iwaki, M. Masuda, K. Namba, S. Ishihara, S. **'Concentration Profiles of Room Temperature Ion Implanted Indium in Silicon'** ***Jap. J. Appl. Phys., 10, 523-525 (1971)*** *Comment : R, dR. 20-80 keV In -> Si*	**1971-Gamo** 1005
1971	Gamo, K. Iwaki, M. Masuda, K. Namba, S. Ishihara, S. **'Enhanced Diffusion and Electrical Properties of Ion Implanted Silicon'** ***Intl. Conf. Ion Implantation in Semiconductors, Ed. by I. Ruge and J. Graul, 459-465 (1971)*** *Comment : R. 20-50 keV Sb, In -> Si*	**1971-Gamo2** 1009

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1971	Gamo, K. Iwaki, M. Masuda, K. Ishihara, S. Kimura, K. **'Concentration Profiles of Ion Implanted Impurities into Silicon'** ***Sci. Pap. Inst. Phys. Chem. Res. (Japan), 65, 19-21 (1971)*** *Comment : R, dR. 20-80 keV In, 20 keV Sb -> Si*	**1971-Gamo3** 0753
1971	Gusev, V. M. Busharov, N. P. Demakov, K. D. Kozlow, Yu. G. **'Effects of Channeling on the Distribution of Electrically Active Boron and Phosphorus Atoms in Silicon Single Crystals'** ***Dokl. Akad. Nauk. Sssr, 19, 319-22 (1971). [Engl. Trans. Sov. Phys. Doklady, 19, 213-15 (1971).*** *Comment : R, dR. 100 keV B, 150 keV P -> Si (Cryst. And Random)*	**1971-Guse** 0671
1971	Moline, R. A. **'Ion-Implanted Phosphorous in Silicon: Profiles using C-V Analysis'** ***J. Appl. Phys., 42, 3553-58 (1971)*** *Comment : R. 200, 300, 600 keV H -> Si*	**1971-Moli** 0952
1971	Moline, R. A. Reutlinger, G. W. **'Phosphorus Channeled in Silicon: Profiles and Electrical Activity'** ***In I. Ruge and J. Graul: Ion Implantation in Semiconductors. Springer, Berlin. p. 58-69 (1971)*** *Comment : R,dR. 100-300 keV P -> Si (Cryst.)*	**1971-Moli2** 0455
1971	Seidel, T. E. **'Distribution of Boron Implanted into Silicon'** ***In I. Ruge and J. Graul: Ion Implantation in Semiconductors. Springer, Berlin. p. 47-57 (1971)*** *Comment : R,dR. 30-300 keV 11B -> Si (Cryst. And Polycryst.)*	**1971-Seid** 0456
1971	Sigurd, D. Domeij, B. **'Critical Angles of Sb and Bi Implanted Si'** ***Phys. Letters, 36A, 81-82 (1971)*** *Comment : R. 40 keV Sb, Bi -> Si ([111], [110], [100])*	**1971-Sigu** 0974
1971	Thompson, D. A. Mackintosh, W. D. **'Stopping Cross Sections for 0.3 - 1.7 MeV Helium Ions in Silicon and Silicion Dioxide.'** ***J. Appl. Phys., 42, 3969-76 (1971)*** *Comment : S. 0.3-L.7 MeV He -> Si, SiO2*	**1971-Thom** 0492
1971	Ziegler, J. F. Crowder, B. L. Kleinfelder, W. J. **'Experimental Evaluation of High Energy Ion Implantation Gradients for Possible Fabrication of a Transistor Pedastal Collector'** ***IBM J. Res. and Dev., 15, 452-456 (1971)*** *Comment : R, dR. 2-4 MeV B, P -> Si*	**1971-Zieg** 1090

Pub. Year | **Authors, Title, Journal Citation and Comments** | **Citation Numb**

1972

Akasaka, Y. Horie, K. Kawazu, S.

'Lateral Spread of Boron Ions Implanted in Silicon'

Appl. Phys. Letters, 21, 128-29 (1972)

Comment : dR(Lateral). 75-250 keV B -> Si

1972-Akas
0836

1972

Broude, C. Engelstein, P. Popp, M. Tandon, P. N.

'Dependence of the Doppler Shift Lifetime Method on Slowing Environment'

Phys. Letters, 39B, 185-187 (1972)

Comment : S. Ne (1 MeV) -> C, Mg, Si, + 32 other materials. Doppler shift attenuation measurements (crude).

1972-Brou
1630

1972

Carter, G. Baruah, J. N. Grant, W. A.

'The Collection of Ions Implanted in Semiconductors: II: Range Distributions Derived from Collection and Sputter-Etch Curves.'

Rad. Effects, 16, 107-114 (1972)

Comment : R. 10-30 keV Kr, Tl -> GaAs, GaP, Ge, Si

1972-Cart
0976

1972

Davidson, S. M.

'Rapid Profile Measurements in Ion Implanted Silicon'

J. Phys. E, 5, 23-26 (1972)

Comment : R. 40 keV B -> Si (Anneal)

1972-Davi
1004

1972

DellaMea, G. Drigo, A. V. LoRusso, S. Mazzoldi, P.

'Indirect Determination of the Energy Loss of Protons Channeled in Silicon Crystals'

Rendiconti Della Academia Nationale Dei Lincei. Classe Di Scienze Fisiche Matematiche E Naturali. Ser. 8,, , 52, No. 5, P. 727-33 (1972)

Comment : S. 1600 keV H -> Si (Cryst.)

1972-Dell
0463

1972

DellaMea, G. Drigo, A. V. LoRusso, S. Mazzoldi, P. Bentini, G. G.

'Transmission Energy Loss of Light Channeled Particles in Thin Silicon Single Crystals'

Rad. Effects, 13, 115-19 (1972)

Comment : S,dS. 0.9-5.0 MeV P, D, He -> Si (Cryst.)

1972-Dell2
0480

1972

Demichelis, F. Liscia, R. Tartaglia, A.

'Range of Fission Fragments in Light Solid Materials'

Nuovo Cimento, 10B, 523-537 (1972)

Comment : R. 100-500 keV Fission Fragments -> Be, C, Al, Si

1972-Demi
1002

1972

Eisen, F. H. Clark, G. J. Bottiger, J. Poate, J. M.

'Stopping Power of Energetic Helium Ions Transmitted through Thin Silicon Crystals in Channeling and Random Directions'

Rad. Effects, 13, 93-100 (1972)

Comment : S,dS. 0.1-18 MeV He -> Si (Cryst.). Chan. And Random.

1972-Eise
0482

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1972	Foster, C. Kool, W. H. VanDerWeg, W. F. Roosendaal, E. **'Random Stopping Power for Protons in Silicon'** ***Rad. Effects, 16, 139-40 (1972)*** *Comment : S. 120 keV H -> Si*	**1972-Fost** 0466
1972	Gittins, R. P. Morgan, D. V. Dearnaley, G. **'The Application of the Ion Microprobe Analyzer for the Measurements of the Distribution of Boron Ions Implanted into Silicon Crystals'** ***J. Phys. D: Appl. Phys., 5, 1654-63 (1972)*** *Comment : R, dR. 200 keV Na, 110-400 keV B -> Si (Cryst. Chann. And Random)*	**1972-Gitt** 0616
1972	Hart, R. R. Lee, D. H. March, O. J. **'Enhanced Migration of Implanted Sb and In in Si Covered with Evaporated Al'** ***Appl. Phys. Letters, 20, 76-77 (1972)*** *Comment : R. 180 keV Sb, In -> Al, Si*	**1972-Hart** 1001
1972	Krylow, J. Rosinski, W. Saczuk, K. **'Study of the Concentration Profiles of Phosphorus and Boron Implanted into Silicon'** ***Electron Tech., 5, 109-117 (1972)*** *Comment : R. 30 keV P, 40 keV B -> Si*	**1972-Kryl** 0992
1972	Maul, J. Schulz, F. Wittmaack, K. **'Determination of Implantation Profiles in Solids by Secondary Ion Mass Spectrometry'** ***Phys. Letters A, 41, 177-78 (1972)*** *Comment : R. dR. 20-22 keV 11B -> Si (Amorphous)*	**1972-Maul** 0019
1972	Minear, R. L. Nelson, D. G. Gibbons, J. F. **'Enhanced Diffusion in Si and Ge by Light Ion Implantation'** ***J. Appl. Phys., 43, 3468-3480 (1972)*** *Comment : R, dR. 70-150 keV H, D, H2 -> Si, Ge*	**1972-Mine** 0999
1972	Morabito, J. M. Tsai, J. C. **'In-Depth Profiles of Phosphorus Ion-Implanted Silicon by Auger Spectroscopy and Secondary Ion Emission'** ***Surf. Sci., 33, 422-426 (1972)*** *Comment : R. 50 keV P -> Si*	**1972-Mora** 0988
1972	Nishi, H. Sakurai, T. Furuya, T. **'Investigation of Boron Implanted Silicon by Backscattering Method. Defect and Impurity Distribution.'** ***Fujitsu Sci. and Tech. J., 8, 123-35 (1972)*** *Comment : R, dR. 100 keV B -> Si*	**1972-Nish** 0690

1972

Pavlov, P. V. Zorin, E. I. Tetel'Baum, D. I. Baranova, A. S. Vasil'Ev, V. K.

'On the Influence of Channeling and Anomalous Diffusion on the Profiles of Implanted Phosphorus and Boron Atoms Silicon'

Rad. Effects, 13, 153-155 (1972)

Comment : R. 40-100 keV P, B -> Si

1972-Pavl
1011

1972

Reddi, V. G. Sanbury, J. D.

'Channeling of Phosphorus Ions in Silicon'

Appl. Phys. Letters, 20, 30-31 (1972)

Comment : R,dR. 30-600 keV 31P -> Si (Cyrst.)

1972-Redd
0452

1972

Schwuttke, G. H. Brack, K. Gorey, E. F. Kahan, A. Lowe, L. F.

'Formation and Annealing of Isolation Regions in Silicon through Si Bombardment'

Phys. Stat. Sol. A, 14, 107-113 (1972)

Comment : R,dR. Si (1 MeV) -> Si One of the earliest MeV implantation papers.

1972-Schw
2129

1972

Sebilotte, P. Badanoin, M. Ndocko, V. B. Siffert, V.

'Low Energy Boron Implantation Profiles in Silicon from Junction Depth Measurements'

Rad. Effects, 7, 7-15 (1972)

Comment : R,dR. 15 keV B -> Si

1972-Sebi
0459

1972

Sone, K. Fukusawa, F.

'Transmission of Fast Protons through Si Single Crystals'

Mem Fac. Eng. Kyoto Univ., 34, 325-32 (1972)

Comment : S, dS. 3 MeV H -> Si (Cryst.)

1972-Sone
0693

1972

Wagner, S.

'Diffusion of Boron from Shallow Ion Implants in Silicon'

J. Electrochem. Soc., 119, 1570-1575 (1972)

Comment : R, dR. 30 keV B -> Si [111]

1972-Wagn
0990

1972

WestmorelandIii, J. E.

'Channeling Effect Analysis of Lattice Disorder in Boron Implanted Silicon'

Ph.D. Thesis, Cal. Inst. Tech., Unpublished (1972)

Comment : R, dR. 200, 300 keV B -> Si

1972-West
1289

1972

Ziegler, J. F. Crowder, B. L. Cole, G. W. Baglin, J. E. E. Masters, B. J.

'Boron Atom Distributions in Ion-Implanted Silicon by the (n,4He) Nuclear Reaction'

Appl. Phys. Letters, 21, 16-18 (1972)

Comment : R,dR. 40-500 keV B -> Si

1972-Zieg
0453

1973 Akasaka, Y. Horie, K. **1973-Akas** 0541

'Channeling Analysis and Electrical Behavior of Boron Implanted Silicon'

B.L. Crowder (Ed): Ion Implantation in Semiconductors and Other Materials. Plenum. N. Y. 145-57 (1973)

Comment : R,dR. 100 keV 11B -> Si

1973 Akasaka, Y. Horie, K. Yoneda, K. Sakurai, T. Nishi, H. **1973-Akas2** 0692

'Depth Distribution of Defects and Impurities in 100-keV B+ Ion Implanted Silicon'

J. Appl. Phys., 44, 220-24 (1973)

Comment : R, dR. 100 keV B -> Si

1973 Bauer, L. -O. Macpherson, M. R. Robinson, A. T. Dill, H. G. **1973-Baue** 1287

'Properties of Silicon Implanted with Boron Ions through Thermal Silicon Dioxide'

Solid-State Elec., 16, 289-300 (1973)

Comment : R, dR. B (40-100 keV) ->Si Through SiO2

1973 Blood, P. Dearnaley, G. Wilkens, M. A. **1973-Bloo** 0546

'The Depth Distribution of Phosphorus Ions Implanted into Silicon Crystals'

B.L. Crowder (Ed): Ion Implantation in Semiconductors and Other Materials. Plenum. N. Y. 75-85 (1973)

Comment : R,dR. 40-120 keV 32P -> Si (Cryst. And Amorph.)

1973 Bottiger, J. Eisen, F. H. **1973-Bott** 0507

'On Conversion from an Energy Scale to a Depth Scale in Channeling Experiments'

Thin Solid Films, 19, 239-246 (1973)

Comment : S. 0.2-0.4 MeV H -> Si (Cryst.)

1973 Brack, K. Gorey, E. Schwuttke, G. H. **1973-Brac** 2134

'Damage Profiles in High Energy C Bombarded Silicon'

Crystal Latt. Defects, 4, 109-121 (1973)

Comment : R. C (1 - 2 MeV) -> Si

1973 Bulgakov, Yu. V. Nikolaev, V. S. Rogachev, Yu. V. **1973-Bulg** 1284

'Anomalous Energy Loss During Passage of Fast Boron Ions through Plane Channels in Single-Crystal Silicon'

Fiz. and Khim. Obrab. Mater. (Ussr), 5, 54-8 (1973)

Comment : S. B (7.7 MeV) -> Si (111) Channeled

1973 Chu, W. K. Crowder, B. L. Mayer, J. W. Ziegler, J. F. **1973-Chu 2** 0539

'Ranges and Distributions of Ions Implanted into Dielectrics'

B.L. Crowder (Ed): Ion Implantation in Semiconductors and Other Materials. Plenum. N. Y. 225-41 (1973)

Comment : R.dR. (140-300 keV) Zn, Ga, As, Se, Cd, Te, Zn -> Si, Si3N4, Al2O3

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1973	Chu, W. K. Ziegler, J. F. Mitchell, I. V. Mackintosh, W. D. **'Energy-Loss Measurements of 4He Ions in Heavy Metals'** ***Appl. Phys. Letters, 22, 437-39 (1973)*** *Comment : S. 2.0 MeV He -> Al, Si, V, Fe, Co, Ni, Cu, In, Ge, Mo, Sb, Te, Gd, Hf, Ta, W, Ir, Pt, Au, Pb*	**1973-Chu 3** 0124
1973	Combasson, J. L. Bernard, J. Guernet, G. **'Physical Profile Measurements in Insulating Layers using the Ion Analyzer'** ***B.L. Crowder (Ed): Ion Implantation in Semiconductors and Other Materials. Plenum. N. Y. 285-94 (1973)*** *Comment : R,dR. 60, 100 keV B -> SiO2; 20, 40 keV B -> Si3N4; 60 keV B -> Si (Amorphous)*	**1973-Comb** 0537
1973	Crowder, B. L. Ziegler, J. F. Cole, G. W. **'The Influence of the Amorphous Phase on Boron Atom Distributions in Ion Implanted Silicon'** ***B.L. Crowder (Ed): Ion Implantation in Semiconductors and Other Materials. Plenum. N. Y. 257-66 (1973)*** *Comment : R,dR. 50-150 keV 10B -> Si. (Cryst. And Amorph.)*	**1973-Crow** 0538
1973	DellaMea, G. Drigo, A. V. LoRusso, S. Mazzoldi, P. Bentini, G. G. **'Axial- to Planar-Channeling Transition'** ***Phys. Rev. B, 7, 4029-4041 (1973)*** *Comment : R. 1-2.8 MeV H -> Si*	**1973-Dell** 0961
1973	Feng, J. S. -Y. Chu, W. K. Nicolet, M. -A. Mayer, J. W. **'Relative Measurements of Stopping Cross Section Factors by Back-Scattering'** ***Thin Solid Films, 19, 195-204 (1973)*** *Comment : S (1-2 MeV) He -> Au, Ag, Cu, Al, Si. Relative Stopping*	**1973-Feng** 0503
1973	Furukawa, S. Matsumura, H. **'Backscattering Study on Lateral Spread of Implanted Ions'** ***Appl. Phys. Letters, 22, 97-98 (1973)*** *Comment : R, dR, dR(Lateral). 180 keV Kr -> Si*	**1973-Furu** 0125
1973	Furukawa, S. Matsumura, H. Ishiwara, H. **'Back-Scattering Study of Heavy-Ion Distribution in Semiconductors'** ***Thin Solid Films, 19, 399-406 (1973).*** *Comment : R,dR,dR(Lateral). 180 keV Kr -> Si*	**1973-Furu2** 0510
1973	Furukawa, S. Matsumura, H. **'Theoretical and Experimental Studies of Lateral Spread of Implanted Ions'** ***B.L. Crowder (Ed): Ion Implantation in Semiconductors and Other Materials. Plenum. N. Y. 193-202 (1973)*** *Comment : R,dR,dR(Lateral). 50 keV Ar; 100, 180 keV Kr -> Si*	**1973-Furu3** 0540

Pub. Year | Authors, Title, Journal Citation and Comments | Citation Numb

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1973

Gamo, K. Iwaki, M. Masuda, K. Namba, S. Ishihara, S.

'Enhanced Diffusion and Lattice Location of Indium and Gallium Implanted in Silicon'

Jap. J. Appl. Phys., 12, 735-741 (1973)

Comment : R. 45 keV In, Ga ->Si

1973-Gamo
0993

1973

Gibbons, J. F.

'Acceptor Profiles Obtained by Diffusive Redistribution of Implanted Impurities During Annealing'

Appl. Phys. Letters, 23, 49-51 (1973)

Comment : R. 50 keV B -> Si

1973-Gibb
0994

1973

Gibbons, J. F. Mylroie, S.

'Estimation of Impurity Profiles in Ion-Implanted Amorphous Targets using Joined Half-Gaussian Distributions'

Appl. Phys. Letters, 22, 568-569 (1973)

Comment : R. 120 keV Sb, 60 keV B -> Si

1973-Gibb2
0996

1973

Golanski, A. Dybczynski, R.

'Implantation of Ions. Ii. Study on the Distributions of Effective Ranges of Phosphorus Atoms Implanted into Silicon Monocrystal (In Polish).'

Nukleonika, 18, 351-66 (1973)

Comment : R, dR. 16-60 keV P -> Si

1973-Gola
0702

1973

Guerdtsiteli, I. G. Guldamashvili, A. I. Disamidze, E. M. Zaslavsky, S. A. Kalinin, A. N.

'Implantation Angle Influence on Penetration of Boron Channeled Ions into Silicon'

Rad. Effects, 19, 171-74 (1973)

Comment : R, dR. 30-200 keV B -> Si (Cryst.)

1973-Guer
0620

1973

Guseva, M. T. Mansurova, A. N.

'Radiation-Enhanced Diffusion of Boron in Germanium During Ion Implantation'

Rad. Effects, 20, 207-10 (1973)

Comment : R,dR. 30 keV B -> Si

1973-Guse
0806

1973

Hofker, W. K. Werner, H. W. Oosthoek, D. P. DeGrefte, H. A. M.

'Influence of Annealing on the Concentration Profiles of Boron Implantations in Silicon'

Applied Phys., 2, 265-78 (1973)

Comment : R, dR. 70 keV B -> Si

1973-Hofk
0006

1973

Hofker, W. K. Werner, H. W. Oosthoek, D. P. DeGrefte, H. A. M.

'Profiles of Boron Implantation in Silicon Measured by Secondary Ion Mass Spectroscopy'

Rad. Effects, 17, 83-90 (1973)

Comment : R. dR. 30-75 keV B -> Si

1973-Hofk2
0017

1973
Hofker, W. K. Werner, H. W. Oosthoek, D. D. DeGrefte, H. A. M.
'Experimental Analysis of Concentration Profiles of Boron Implanted into Silicon'
B.L. Crowder (Ed): Ion Implantation in Semiconductors and Other Materials. Plenum. N. Y. 133-45 (1973)
Comment : R,dR. 30-70 keV B -> Si
1973-Hofk3
0542

1973
Iwaki, M. Gamo, K. Masuda, K. Namba, S. Ishihara, S.
'Concentration Profiles of Arsenic Implantated in Silicon'
B.L. Crowder (Ed): Ion Implantation in Semiconductors and Other Materials. Plenum. N. Y. 111-18 (1973)
Comment : R,dR. 35-130 keV As -> Si
1973-Iwak
0544

1973
Kelley, J. G. Sellers, B. Hanser, F. A.
'Energy-Loss and Stopping Power Measurements Between 2 and 10 MeV/amu for 12C, 14N, and 16O in Silicon'
Phys. Rev. B, 8, 103-06 (1973)
Comment : S. 24-120 MeV C, 28-140 MeV N, 32-160 MeV O -> Si (Cryst?)
1973-Kell
0485

1973
Kostka, A. Kalbitzer, S.
'Integrated dE-E Detector System made by Ion Implantation'
Appl. Phys. Letters, 23, 704-706 (1973)
Comment : R. B (8 MeV), P (6 keV) -> Si
1973-Kost
2130

1973
Kostka, A. Kalbitzer, S.
'Electrical Properties of Silicon Implanted with Boron Ions of MeV Energy'
Rad. Effects, 19, 77-82 (1973)
Comment : R. B (3-8 MeV) -> Si
1973-Kost2
2131

1973
Lewis, R. K. Morabito, J. M. Tsai, J. C. C.
'Primary Oxygen Ion Implantation Effects on Depth Profiles by Secondary Ion Emmision Mass Spectrometry'
Appl. Phys. Letters, 23, 260-261 (1973)
Comment : R. 4.5 keV O, Ar -> Si
1973-Lewi
0995

1973
Lin, W. K. Olson, H. G. Powers, D.
'Alpha-Particle Stopping Cross Sections of Silicon and Germanium'
J. Appl. Phys., 44, 3631-34 (1973)
Comment : S. 0.3-2.0 MeV He -> Si, Ge (Amorph.)
1973-Lin
0497

1973
Mezey, G. Szokefalvi-Nagy, Z. Badinka, C. S.
'Measurement of the Boron Distribution in 10B-Implanted Silicon by the (n,alpha) Nuclear Reaction'
Thin Solid Films, 19, 173-175 (1973)
Comment : R, dR. 10-40 keV 10B -> Si
1973-Meze
0001

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1973	Okabayashi, H. Shinoda, D. **'Lateral Spread of 31P and 11B Ions Implanted in Silicon'** ***J. Appl. Phys., 44, 4220-21 (1973)*** *Comment : R, dR, dR(Lateral). 145, 260 keV 31P; 80, 150 keV 11B -> Si*	**1973-Okab** 0835
1973	Reddi, V. G. K. Sansbury, J. D. **'Channeling and Dechanneling of Ion-Implanted Phosphorus in Silicon'** ***J. Appl. Phys., 44, 2951-63 (1973)*** *Comment : R,dR. 30-900 keV 31P -> Si (Cryst.)*	**1973-Redd** 0498
1973	Reid, I. Kelly, R. **'The Use of Dissolution Curves to Determine Amorphization Depths and Damage Ranges in Silicon'** ***Rad. Effects, 17, 253-260 (1973)*** *Comment : R. 10, 40 keV Kr -> Si*	**1973-Reid** 1171
1973	Schulz, F. Wittmaack, K. Maul, J. **'Implications in the Use of Secondary Ion Mass Spectroscopy to Investigate Impurity Concentration Profiles in Solids'** ***Rad. Effects, 18, 211-15 (1973)*** *Comment : R, dR. 20 keV 11B -> Si*	**1973-Schu** 0005
1973	Schwartz, G. Trapp, M. Schimko, R. Butzke, G. Rogge, K. **'Concentration Profiles of Implanted Boron Ions in Silicon from Measurements with the Ion Microprobe'** ***Phys. Stat. Sol. A, 17, 653-58 (1973)*** *Comment : R, dR. 50-300 keV B -> Si*	**1973-Schw** 0128
1973	Schwettmann, F. N. **'Enhanced Diffusion During the Implantation of Arsenic in Silicon'** ***Appl. Phys. Letters, 22, 570-72 (1973)*** *Comment : R, dR. 120 keV As -> Si*	**1973-Schw2** 0012
1973	Sellers, B. Hanser, A. Kelley, J. G. **'Energy Loss and Stopping Power Measurements Between 2 and 10 MeVamu for 3He and 4He in Silicon.'** ***Phys. Rev. B, 8, 98-102 (1973)*** *Comment : S. 6-30 MeV 3He, 8-40 MeV 4He -> Si (Cryst.?)*	**1973-Sell** 0484
1973	Tsai, J. C. Morabito, J. M. Lewis, R. K. **'Arsenic Implanted and Implanted Diffused Profiles in Silicon using Secondary Ion Emission and Differential Resistance'** ***B.L. Crowder (Ed): Ion Implantation in Semiconductors and Other Materials. Plenum. N. Y. 87-97 (1973)*** *Comment : R,dR. 40 keV As -> Si*	**1973-Tsai** 0545

1973
Wittmaack, K. Maul, J. Schulz, F.
'Energy Dependence and Annealing Behaviour of Boron Range Distributions in Silicon'
B.L. Crowder (Ed): Ion Implantation in Semiconductors and Other Materials. Plenum. N. Y. 119-31 (1973)
Comment : *R,dR. 10-250 keV B -> Si*
1973-Witt
0543

1973
Wittmaack, K. Schulz, F. Maul, J.
'Nongaussian Range Profiles in Amorphous Solids'
Phys. Letters A, 43, 477-78 (1973)
Comment : *R, dR. 100 keV 11B -> Si (Amorphous)*
1973-Witt2
0018

1973
Ziegler, J. F. Brodsky, M. H.
'Specific Energy Loss of 4He Ions in Silicon (Amorphous, Polycrystalline, and Single Crystal)'
J. Appl. Phys., 44, 188-96 (1973)
Comment : *S. 0.42-2.75 MeV He -> Si*
1973-Zieg
0474

1973
Zohta, Y.
'Rapid Determination of Semiconductor Doping Progiles in Mos Structure'
Solid-State Elec., 16, 124-126 (1973)
Comment : *R. 40 keV B -> SiO2, Si*
1973-Zoht
0989

1974
Avdeichikov, V. V. Ganza, E. A. Lozhkin, O. V.
'Energy-Loss Fluctuation of Heavy Charged Particles in Silicon Absorbers'
Nucl. Inst. Methods, 118, 247-52 (1974)
Comment : *dS. 7.7 MeV He, 255 MeV Ar -> Si*
1974-Avde
0628

1974
Baglin, J. E. E. Ziegler, J. F.
'Tests of Bragg's Rule for Energy Loss of 4He Ions in Solid Compounds'
J. Appl. Phys., 45, 1413-1415 (1974)
Comment : *S. He (2 MeV) -> Si, Rh, Hf, Al, W, C, and many compounds*
1974-Bagl
1583

1974
Baranova, E. K. Gusev, V. M. Streltsov, L. N.
'Distribution of Defects with Depth in Silicon Irradiated with 80 keV Lithium Ions'
Sov. Phys. Semicond., 7, 1239-1240 (1974)
Comment : *dR. 80 keV Li -> Si*
1974-Bara
0987

1974
Bayadilov, E. M. Vavilov, V. S. Katsaurov, L. N. Krasnopevtsev, V. V. Milyutin, Y. V.
'Heat Treatment-Induced Redistribution of the Concentration of Implanted Li Ions in Silicon'
Sov. Phys. Semicond., 7, 1225-1226 (1974)
Comment : *R. 40 keV Li -> Si (With Anneal)*
1974-Baya
0986

1974 Blood, P. Dearnaley, G. Wilkins, M. A. **1974-Bloo** 0985

'The Origin of Non-Gaussian Profiles in Phosphorus-Implanted Silicon'

J. Appl. Phys., 45, 5123-5128 (1974)

Comment : R, dR. P -> Si ([110], [100])

1974 Blood, P. Dearnaley, G. Wilkens, M. **1974-Bloo2** 0706

'The Depth Distribution of Phosphorus Ions Implanted into Silicon Crystals'

Rad. Effects, 21, 245-51 (1974)

Comment : R, dR. 40-120 keV 32P -> Si (Cryst. And Amorph.)

1974 Bogancs, J. Deme, S. Gyulai, J. Nagy, A. Nazarov, V. M. **1974-Boga** 0859

'A Method for the Determination of Boron Ranges in Ion Implanted Silicon by the 10B(n, Alpha) Nuclear Reaction'

Joint Institute for Nuclear Research. Dubna, Report No. P. 14-8295 (In Russian) (1974)

Comment : R. 20-80 keV B -> Si

1974 Bulgakov, Yu. V. Nikolaev, V. S. Shulga, V. I. **1974-Bulg** 0668

'The Experimental Determination of the Impact Parameter Dependence of Inelastic Energy Loss of Channeled Ions'

Phys. Letters A, 46, 477-78 (1974)

Comment : S, dS. 1.15, 1.75 MeV H, 5.7 MeV N -> Si (Cryst.)

1974 Burkhardt, F. Mertens, A. Wagner, C. **1974-Burk** 0991

'Concentration Profiles of Implanted Phosphorus in Silicon'

Phys. Stat. Sol. A, 22, K45-47 (1974)

Comment : R. 50 keV P -> Si

1974 Castaing, C. Baruch, P. Picard, C. **1974-Cast** 0949

'Mesures Experimentales De La Penetration Des Protons Dans Le Silicum'

Le Vide, 171 Supplt, 61 (1974)

Comment : R. 200-600 keV H -> Si. Ranges From Pit-Depth After Blistering Of Silicon.

1974 Cembali, F. Galloni, R. Mousty, F. Rosa, R. Zignani, F. **1974-Cemb** 0705

'Doping and Radiation Damage Profiles in Silicon Along the [110] Axis'

Rad. Effects, 21, 255-64 (1974)

Comment : R, dR. 200 keV P -> Si (Cryst.)

1974 Drum, C. M. **1974-Drum** 1279

'Diffusion of Ion Implanted Antimony and Arsenic in Silicon'

J. Electrochem. Soc., 121, 93C (1974)

Comment : R, dR. Sb, As (30-80 Kev) -> Si

1974 Grant, W. A. Williams, J. S. Dodds, D. **1974-Gran** 0843

'Measurement of Projected and Lateral Range Parameters for Low Energy Heavy Ions in Silicon by Rutherford Backscattering'

Meyer, G. Linker and F. Kappeler (Ed.):Ion Beam Surface Layer Analysis, Plenum, N. Y., P. 235-44 (1974)

Comment : R, dR, dR(Lateral). 10-80 keV Pb, 50-400 keV Bi, 40 keV Ar, Cu, Kr, Cd, Al, Dy, W -> Si

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1974	Greene, J. E. Sequeda-Osorio, F. Streetman, B. G. Noonan, J. R. Kirpatrich, G. G. **'Measurement of Boron Impurity Profiles in Si using Glow Discharge Optical Spectroscopy'** ***Appl. Phys. Letters, 25, 435-38 (1974)*** *Comment : R, dR. 120 keV B -> Si*	**1974-Gree** 0839
1974	Grob, J. J. Grob, A. Siffert, P. **'Evaluation of Heavy Ion Energy Losses in Silicon Due to a Channelling Phenomena'** ***Vide (France), 29, 374-9 (1974)*** *Comment : S, dS. (400-1900 keV) N, Si -> Si*	**1974-Grob** 1266
1974	Guivarc'H, E. Ligeon A. **'A New Utilization of 11B Ion Beams: Hydrogen Analysis by 1H(11B,alpha)alpha,alpha Nuclear Reaction'** ***Rad. Effects, 22, 101-105 (1974)*** *Comment : R, dR. 10 keV H -> Si*	**1974-Guiv** 0801
1974	Hofker, W. K. Werner, H. Oosthoek, D. P. Koeman, N. J. **'Boron Implantations in Silicon: A Comparison of Charge Carrier and Boron Concentration Profiles'** ***Appl. Phys., 4, 125-33 (1974)*** *Comment : R, dR. 70 keV B -> Si*	**1974-Hofk** 0614
1974	Muller, H. Kranz, H. Ryssel, H. Schmid, K. **'Electrical and Backscattering Measurements of Arsenic Implanted Silicon'** ***Appl. Phys., 4, 115-23 (1974)*** *Comment : R. 150-200 keV As -> Si (Cryst.)*	**1974-Mull** 0615
1974	Okabayashi, H. Daizaburo, S. **'Range and Standard Deviation of Ion-Implanted Phosphorus and Boron in Silicon'** ***NEC Res. and Dev., 35, 10-14 (1974)*** *Comment : R, dR. 50-260 keV P, B -> Si*	**1974-Okab** 0982
1974	Okabayashi, H. Shinoda, D. **'Range and Standard Deviation of Ion-Implanted Phosphorus in Silicon'** ***Jap. J. Appl. Phys., 13, 1187-88 (1974)*** *Comment : R. 50-145 keV 31P -> Si*	**1974-Okab2** 0638
1974	Pan, E. Fang, F. F. **'Lateral Spread of Ion Implanted Impurities in Silicon'** ***J. Appl. Phys., 45, 2801-2803 (1974)*** *Comment : R. B, P (20-70 keV) -> Si One of the earliest lateral-spread range measurements.*	**1974-Pan** 2140

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1974	Pavlov, P. V. Popov, Y. S. Belich, T. V. **'Distribution of Recombination Centers Produced by Bombardment of Silicon with Moderate-Energy Ions'** ***Sov. Phys. Semicond., 8, 602-603 (1974)*** *Comment : R. 50 keV N, Ar -> Si*	**1974-Pavl** 0983
1974	Pistryak, V. M. Tetelbaum, D. I. Kozlov, V. F. Vasilev, V. K. Zorin, E. I. **'Influence of Amorphization on the Distribution of Boron Introduced into Silicon by Ion Bombardment'** ***Sov. Phys. Semicond., 7, 1325-1326 (1974)*** *Comment : R. 100 keV B -> Si*	**1974-Pist** 0981
1974	Prince, J. L. Schwettmann, F. N. **'Diffusion of Boron from Implanted Sources Under Oxidizing Conditions'** ***J. Electrochem. Soc., 121 705-710 (1974)*** *Comment : R, dR. 80 keV B -> Si*	**1974-Prin** 0979
1974	Ryssel, H. Muller, H. Schmid, K. **'Damage Dependent Electrical Activation of Boron Implanted Silicon'** ***Applied Phys., 3, 321-24 (1974)*** *Comment : R, dR. 34 keV B -> Si*	**1974-Ryss** 0825
1974	Schmid, K. Fischer, G. Muller, H. Ryssel, H. **'Experimental Data About Dechanneling and Channel Stopping Power'** ***Rad. Effects, 23, 145-49 (1974)*** *Comment : S. 1 MeV He -> Si (Cryst.)*	**1974-Schm** 0519
1974	Schulz, M. Goetzberger, A. Franz, I. Langheinrich, W. **'Controlled Gold Doping of Silicon by using Ion Implantation'** ***Appl. Phys., 3, 275-280 (1974)*** *Comment : R. 110 keV Au -> Si*	**1974-Schu** 0978
1974	Williams, J. S. **'Range and Stopping Power Effects Obtained from High Resolution Rutherford Backscattering Analysis of Implanted Targets'** ***Rad. Effects, 22, 211-13 (1974)*** *Comment : R, dR. 40 keV Pb -> Si*	**1974-Will** 0684
1975	Barcz, A. Turos, A. Wielunski, L. Rosinski, W. Wojtowicz-Natanson, B. **'Depth Distribution of Silver Ions Implanted in Si and SiO2'** ***Rad. Effects, 25, 91-96 (1975)*** *Comment : R, dR. 20-140 keV 107Ag -> Si, SiO2*	**1975-Barc** 0718
1975	Biersack, J. Fink, D. **'Implantation of Boron and Lithium in Semiconductors Metals'** ***Ion Implantation in Semiconductors, Namba (ed.), Plenum, N. Y. 211-18 (1975)*** *Comment : R, dR. 50-150 keV 10B -> Si*	**1975-Bier** 0748

1975 Bill, U. Sizmann, R. Varelas, C. Rehn, K. E. **1975-Bill**
'Transition of Axial to Planar Channeling' 0883
Rad. Effects, 27, 59-66(1975)
Comment : S, dS. 100 MeV S -> Si (Cryst.)

1975 Blank, P. Wittmaack, K. **1975-Blan**
'Range Parameter Distortion in Heavy Ion Implantation' 0751
Phys. Letters A,54, 33-34 (1975)
Comment : R, dR. 20-50 keV Xe -> Si

1975 Buhl, R. Huber, W. K. Lobach, E. **1975-Buhl**
'Messung von Konzentrationsprofilen Dunner Schichten Mit der Sekundarionen-Massenspektrometrie (Sims)' 0789
Vakuum-Technik, 24, 189-94 (1975)
Comment : R. 60, 100 keV B -> Si

1975 Bulgakov, Yu. V. Nikolaev, V. S. Shulga, V. I. **1975-Bulg**
'Impact-Parameter Dependence of Inelastic Energy Losses for He and N Ions Channeled in Si' 0799
Phys. Stat. Sol. A, 31, 341-50 (1975)
Comment : S, dS. 1.3, 6.6 MeV He, 4.4 MeV N -> Si (Cryst.)

1975 Dearnaley, G. Gard, G. A. Temple, W. Wilkins, M. A. **1975-Dear**
'Depth Distribution of Gallium Ions Implanted into Silicon Crystals' 0713
Appl. Phys. Letters, 27, 17-18 (1975).
Comment : R, dR. 40 keV 72Ga -> Si (Cryst.)

1975 DellaMea, G. Drigo, A. V. LoRusso, S. Mazzoldi, P. Bentini, G. G. **1975-Dell**
'Transmission Energy Loss of Protons Channeled in Thin Silicon Single Crystals of Medium Energy' 0574
Datz, B. R. Appleton, C. D. Moak (Ed.): Atomic Collisions in Solids. Plenum N. Y., 75-76 (1975)
Comment : S. 50-300 keV H -> Si (Cryst.) Chann. To Random Ratio

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1975 Dikii, N. P. Matyash, P. P. Skakun, N. A. **1975-Diki**
'Profiles of Radiation Damage and Implanted Boron in Silicon' 1022
Sov. Phys. Semicond., 9, 395-96 (1975)
Comment : R. 50 keV B -> Si

1975 Eisen, F. H. Bottiger, J. **1975-Eise**
'Transmission Energy Spectra of Channeled Protons Scattered in Thin Silicon Films' 0579
Atomic Collisions in Solids, Plenum Press, 919-27 (1975)
Comment : S,dS. 200, 400 keV H -> Si (Cryst.)

1975 Feuerstein, A. Kalbitzer, S. Oetzmann, H. **1975-Feue**
'Range Parameters of Heavy Ions at 10 and 35 keV in Silicon' 0837
Phys. Letters A, 51, 165-66 (1975)
Comment : R, dR. 10-35 keV Ge, As -> Si

1975
Gashtol'D, V. N. Gerasimenko, N. N. Dvurechenskii, A. V. Smirnov, L. S.
'Profiles of Defects Produced by the Implantation of Ions in Silicon'
Sov. Phys. Semicond., 9, 551-553 (1975)
Comment : R. Profiles Of Defects (40-250 keV) Ar, B, P -> Si
1975-Gash
1023

1975
Gotz, V. G. Klinge, K. D. Schwabe, F.
'Measurement of the Energy Loss in Thin Silicon Single Crystals'
Exp. Tech. Phys., 23, 167-169 (1975)
Comment : S. 0.7-1.6 MeV H -> Si
1975-Gotz
1017

1975
Gotz, G. Klinge, K. D. Finger, U.
'A Combination of Dechanneling and Energy Measurements of Protons in Thin Silicon Single Crystals.'
Atomic Collisions in Solids, Plenum Press, 693-716 (1975)
Comment : S. 0.7-1.8 MeV H -> Si (Cryst.) Chann. To Random Ratio.
1975-Gotz2
0577

1975
Grob, J. J. Grob, A. Pape, A. Siffert, P.
'Energy Loss of Heavy Ions in Nuclear Collisions in Silicon'
Phys. Rev. B, 11, 3274-79 (1975)
Comment : S, dS, Eta(Epsilon). 0.3-2 MeV N, Si -> Si (Cryst.)
1975-Grob
0710

1975
Hendrickson, T. E.
'Ion Implanted Profiles from Two Point Spreading Resistance Measurements'
J. Electrochem. Soc., 122, 1539-1541 (1975)
Comment : R. 150, 300 keV B -> Si ([100])
1975-Hend
1019

1975
Hirao, T. Ohzone, T. Takayanagi, S. Horumi, H.
'Ion Implantation in Polycrystalline Silicon'
Ion Implantation in Semiconductors, Namba (ed.), Plenum, N. Y. 599-604 (1975)
Comment : R, dR. 50-150 keV B -> Si
1975-Hira
0750

1975
Hofker, W. K.
'Implantation of Boron in Silicon'
Philips Res. Repts. No. 8, P. 1-121 (1975)
Comment : R,dR. 30-800 keV B -> Si (Amorph., Polycryst.)
1975-Hofk
0802

1975
Hofker, W. K. Oosthoek, D. P. Koeman, N. J. DeGrefte, H. A. M.
'Concentration Profiles of Boron Implantations in Amorphous and Polycrystalline Silicon'
Rad. Effects, 24, 223-31 (1975)
Comment : R,dR. 30-200 keV B -> Si (Polycryst.), 70-800 keV B -> Si (Amorph.)
1975-Hofk2
0520

1975
Hurrle, A. Sixt, G.
'Cesium Profiles in Silicon and in SiO2-Si Double Layers as Determined by Sims Measurements'
Applied Phys., 8, 293-302 (1975)
Comment : R. 10-100 keV Cs -> Si
1975-Hurr
0795

1975
Iwaki, M. Gamo, K. Masuda, K. Namba, S. Ishihara, S.
'Comparison Between Concentration Profiles of Arsenic Implanted in Silicon Measured by Means of Neutron Activation Analysis and Radioactive Ion Implantation'
Jap. J. Appl. Phys., 14, 167-68 (1975)
Comment : *R. 45 keV As -> Si*
1975-Iwak
0527

1975
Iwaki, M. Gamo, K. Masuda, K. Namba, S. Ishihara, S.
'Experimental Method for Measuring Both Atom and Carrier Concentration Profiles in the Same Sample of Ion-Implanted Silicon Layers by Radioactive-Ion Implantation'
Nucl. Inst. Methods, 127, 93-98 (1975)
Comment : *R, dR. 45 keV As -> Si*
1975-Iwak2
0716

1975
Iwaki, M. Gamo, K. Masuda, K. Namba, S. Ishihara, S.
'Atom and Carrier Profiles in as Implanted Si'
Ion Implantation in Semiconductors, Namba (ed.), Plenum, N. Y. 163-68 (1975)
Comment : *R, dR. 25 keV As -> Si*
1975-Iwak3
0745

1975
Kiselevich, M. Lyatushinski, A. Zhuk, V. Osipenko, B. P.
'Implantation of Heavy Ions into Silicon Single Crystals'
Fiz. Tverd. Tela, 17, 1080-84 (1975). [Engl. Trans. Sov. Phys. Solid State, 17, 687-89 (1975).
Comment : *R, dR. 45 keV Sr, Ba, Ce, Nd, Eu, Gd, Tb, Er, Tm, Lu -> Si (Cryst. Chann. And Random)*
1975-Kise
0796

1975
Ludvik, S. Scharpen, L. Weawer, H. E.
'Measurement of Arsenic Implantation Profiles in Silicon using Electron Spectroscopic Technique'
Ion Implantation in Semiconductors, Namba (ed.), Plenum, N. Y. 155-62 (1975)
Comment : *R, dR. 25, 40 keV 75As -> Si*
1975-Ludv
0744

1975
Melvin, J. D.
'Energy Loss of Light Ions Channeling in Silicon'
Ph.D., Cal. Inst. Tech., Unpublished (1975)
Comment : *S, dS. 0.5-1.6 MeV H -> Si (110), (111), (211)*
1975-Melv
1271

1975
Melvin, J. D. Tombrello, T. A.
'Energy Loss of Low Energy Protons Channeling in Silicon Crystals'
Rad. Effects, 26, 113-26 (1975)
Comment : *S. 0.5-1.6 MeV H -> Si (Cryst.)*
1975-Melv2
0757

1975
Neuwirth, W. Pietsch, W. Richter, K. Hauser, U.
'Electronic Stopping Cross Sections of Elements and Compounds for Swift Lithium Ions'
Z. Physik A, 275, 209-14 (1975)
Comment : *S. 80-840 keV Li -> Be, B, Al, Ti, Cu, Ta, AlB2, AlB12, B4C, B2O3, BPO4, B4Si, CaB6, CeB6, Crb, Crb2, Cr2B3, H2O, D2O, HBO2, H3BO3, HFB2, KBF4, KBH4, LaB6, LiBH*
1975-Neuw2
0813

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1975	Oetzmann, H. Feuerstein, A. Grahmann, H. Kalbitzer, S. **'Range Parameters of Heavy Ions in Amorphous Targets at LSS-Energies of 0.0006 < Epsilon < 0.3.'** ***Phys. Letters, 55A, 170-172 (1975)*** *Comment : R, dR. 1-60 keV As, Ge, Sb, Au, Bi -> Si, Ge, Al*	**1975-Oetz** 1182
1975	Ohmura, Y. Koike, K. Kobayashi, H. Murakami, K. **'Deviated Gaussian Profiles of Implanted Boron and Deep Levels in Silicon'** ***Ion Implantation in Semiconductors, Namba (ed.), Plenum, N. Y. 183-88 (1975)*** *Comment : R, dR. 60-200 keV 10B, 11B -> Si*	**1975-Ohmu** 0746
1975	Ohmura, Y. Koike, K. **'Evidence for Electronic Stopping in Ion Implantation: Shallower Profile of Lighter Isotope 10B in Si'** ***Appl. Phys. Letters, 26, 221-22 (1975)*** *Comment : R, dR. 50-200 keV 10B, 11B -> Si*	**1975-Ohmu2** 0841
1975	Schuch, R. **'Blocking-Effekte Bei Transmission von Alpha-Teilchen Durch Germanium - und Siliziumkristalle'** ***Z. Physik A, 272, 61-66 (1975)*** *Comment : S. 8.8 MeV He -> Si, Ge (Cryst.)*	**1975-Schu** 0516
1975	Schwuttke, G. H. Brack, K. **'Annealing of High Energy Ion Implantation Damage in Single Crystal Silicon'** ***IBM (East Fishkill, NY) Tecnical Report TR-22.715 (1968)*** *Comment : R. N(1.5-2.0 MeV) -> Si One of the earliest high-energy ion implantation papers.*	**1975-Schw** 2123
1975	Sigmon, T. W. Chu, W. K. Muller, H. Mayer, J. W. **'Analysis of Arsenic Range Distributions in Silicon'** ***Applied Phys., 5, 347-50 (1975)*** *Comment : R, dR. 50-250 keV As -> Si*	**1975-Sigm** 0640
1975	Skakun, N. A. Dikii, N. P. Matyash, P. P. **'Some Characteristics of the Distribution of Radiation Defects Resulting from the Implantation of Boron Ions in Silicon'** ***Sov. Phys. Semicond., 8, 854-855 (1975)*** *Comment : R. 50 keV B -> Si*	**1975-Skak** 0980
1975	Skakun, N. A. Grigorev, A. N. Dikii, N. P. Matyash, P. P. Nikolaichuk, L. I. **'Investigation into the Profile of Radiation Damage in Si using the Elastic Scattering of 4He Ions'** ***Pis'Ma Zh. Tekh. Fiz. (USSR) 1, 203-7 (1975)*** *Comment : R, dR. 80 keV Li -> Si*	**1975-Skak2** 1264

1975 Tsai, J. C. C. Morabito, J. M. — **1975-Tsai** 0743
'In-Depth Profile Detection Limits of Nitrogen in GaP and Nitrogen, Oxygen, and Fluorine in Si by SIMS and AES'
Ion Implantation in Semiconductors, Namba (ed.), Plenum, N. Y. P. 115-24 (1975)
Comment : R, dR. 50 keV N -> GaP, Si; 50 keV O, F -> Si

1975 Williams, J. S. Grant, W. A. — **1975-Will** 0611
'High Resolution Rutherford Backscattering and Its Application to Ion Range and Ion Collectionrad'
Rad. Effects, 25, 55-56 (1975)
Comment : R, dR. 20-80 keV Kr, Xe, Cs, Dy, Au, Pb, Bi -> Si, Al

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1975 Yudin, V. V. Kurinny, V. I. Akimov, Y. S. Karatsyuba, A. P. — **1975-Yudi** 0977
'Spatial Distribution of Defects Produced by Boron Ion Implantation of Silicon'
Rad. Effects, 24, 59-61 (1975)
Comment : R. 40 keV B -> Si

1976 Anand, K. V. El-Dhaher, A. H. G. Sobhy, M. I. — **1976-Anan** 1018
'Distribution Profiles of Boron-Implanted Layers in Silicon using a High Resolution Anodic Oxidation Cell'
Int. J. Elec., 40, 617-623 (1976)
Comment : R. 60-100 keV B -> Si

1976 Armbruster, P. Sistemich, K. Bocquet, J. P. Chauvin, Ch. Glaize, Y. — **1976-Armb** 0863
'Energy Straggling of Heavy Ions (A About 100, E/A About 1 MeV/amu) in Solids and Gases, the Limiting Factor of the Charge Resolving Power of Energy-Loss Detectors'
Nucl. Inst. Methods, 132, 120-32 (1976).
Comment : dS. 90 MeV Kr, Rb -> Si; 84 MeV Y, Zr -> C; 83 MeV Kr -> Ar

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1976 Avdeichikov, V. V. Ganza, E. A. Lozhkin, O. V. — **1976-Avde** 0882
'Energy Resolution of Thin Semiconductor Delta-E Detectors for Alpha Particles and Heavy Ions'
Nucl. Inst. Methods, 131, 61-68 (1976)
Comment : dS. (1-200 MeV) He, C, N, O, Ne, Ar -> Si

1976 Baragiola, R. A. Chivers, D. Dodds, D. Grant, W. A. Williams, J. S. — **1976-Bara** 0873
'Ranges in Silicon of Ions with Atomic Numbers 62 <= Z1 <= 66 at 100 keV'
Phys. Letters A, 56, 371=73 (1976)
Comment : R, dR. 100 keV 152Sm, 153Eu. 157Gd, 159Tb, 164Dy -> Si

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1976 Braun, M. Emmoth, B. Buchta, R. — **1976-Brau** 0886
'Concentration Profiles and Sputtering Yields Measured by Optical Radiation of Sputtered Particles'
Rad. Effects, 28, 77-83 (1976)
Comment : R, dR. 50-120 keV Al -> Ag; 60 keV Na -> Si

1976 Dietrich, H. B. Comas, J. **1976-Diet** 1069
'Anomalous Redistribution of Ion-Implanted Dopants'
Ion Implantation in Semiconductors, Ed. by F. Chernow, J. A. Borders, D. K. Brice, 735-742 (1976)
Comment : R. 60 keV Al -> Si, 100 keV Be -> Si, GaAs

1976 Dietrich, H. B. Plew, L. E. **1976-Diet2** 0861
'19F Range-Energy Curve in Si from 100 keV - 550 keV'
J. Appl. Phys., (1976)
Comment : R. 100-550 keV F -> Si

1976 Dietrich, H. B. Weisenberger, W. H. Comas, J. **1976-Diet3** 0807
'Anomalous Migration of Ion-Implanted Al in Si'
Appl. Phys. Letters, 28, 182-84 (1976)
Comment : R,dR. 60 keV Al -> Si

1976 Emmoth, B. Braun, M. Palenius, H. P. **1976-Emmo** 1070
'Implantation Profiles and Sputtering Studied by Detecting the Optical Radiation from Sputtered Particles Buring Bombardment'
J. Nucl. Mater., 63, 482-486 (1976)
Comment : R, dR. 10 keV Li -> Ag, V, 20 keV Li -> Si, 20-40 keV Li -> Al, 40 keV Ar -> Ag

1976 Grahmann, G. Kalbitzer, S. **1976-Grah** 0871
'Nuclear and Electronic Stopping Powers of Low Energy Ions with Z <= 10 in Silicon'
Nucl. Inst. Methods, 132, 119-23 (1976)
Comment : S. 2-60 keV H, He, B, C, N, Ne -> Si

1976 Grant, W. A. Dodds, D. Williams, J. S. Christodoulides, C. E. Baragiola, R. A. **1976-Gran** 1013
'Heavy Ion Ranges in Silicon and Aluminum'
Ion Implantation in Semiconductors, Ed. by F. Chernow, J. A. Borders, D. K. Brice, 693-703 (1976)
Comment : R. 0.01 < Epsilon < 0.8 Cr, Ni, Ga, As, Br, Mo, Cs, La, Nd, Dy, Ta, Pt, Au, Pb -> Si, Al

1976 Grant, W. A. Williams, J. S. Dodds, D. **1976-Gran2** 0931
'Measurement of Projected and Lateral Range Parameters for Low Energy Heavy Ions in Silicon by Rutherford Backscattering'
O. Meyer, G. Linker, F. Kappeler (Ed.): Ion Beam Surface Layer Analysis, Plenum, N. Y., 457-69 (1976)
Comment : R, dR, dR (Lateral). 10-80 keV Pb, 50-400 keV Bi, 40 keV Ar, Cu, Kr, Cd, Al, Dy, W -> Si

1976 Grant, W. A. Williams, J. S. Dodds, D. **1976-Gran3** 0887
'Measurement of the Lateral Spread of Heavy Ions Implanted into Silicon'
Rad. Effects, 29, 189-90 (1976)
Comment : dR(Lateral). (10-40 keV) Cu, Cd, Xe, Dy, Kr, W, Pb, Bi -> Si

1976
Grob, A.   Grob, J. J.   Siffert, P.
'Energy Loss and Straggling of Heavy Ions by Nuclear Interactions in Silicon'
Nucl. Inst. Methods, 132, 273-79 (1976)
Comment : S, dS, Eta(Epsilon). 300-2000 keV C, N, O, Ne, Si, S, Ar -> Si
1976-Grob
0780

1976
Hasegawa, S.   Ishiwara, H.   Furukawa, S.   Shimizu, T.
'The Lattice Location of Phosphorus Atoms Implanted into Silicon'
Jap. J. Appl. Phys., 15, 391-92 (1976)
Comment : R. 100 keV P -> Si
1976-Hase
0858

1976
Hirvonen, J. K.   Hubler, G. K.
'Application of a High-Resolution Magnetic Spectrometer to Near-Surface Analysis'
Meyer, G. Linker and F. Kappeler (Ed.):Ion Beam Surface Layer Analysis, Plenum, N. Y., P. 457-69 (1976)
Comment : R, dR. 2-60 keV 209Bi, 60 keV 69Ga -> Si
1976-Hirv
0842

1976
Hoffman, I.   Jager, E.   Muller-Jahreis, U.
'Z1-Dependence of Electronic Energy Straggling of Light Ions'
Rad. Effects, 31, 57 (1976)
Comment : dS. 2 <= Z1 <=10 (10-100 Kev) -> C, Si
1976-Hoff
1259

1976
Kovaleva, E. A.   Korol, V. M.   Merrik, B. R.
'Ranges of Metals in Amorphous Si and Ge'
Elektronnaya Texnika, 2, 33-38 (1976)
Comment : R, dR. 10-200 keV Li, Na, K, Rb, Cs -> Si, Ge, Al, Ni
1976-Kova
0944

1976
Krautle, H.
'Study of the Sputtering Process with Rutherford Backscattering'
Nucl. Inst. Methods, 137, 553-7 (1976)
Comment : R, dR. 50 keV Au -> Al, 5-30 keV B -> Si
1976-Krau
0914

1976
Kudoh, O.   Uda, K.   Ikushima, Y.   Kamoshida, M.
'Impurity Profiles Within a Shallow P-N Junction by a New Differential Spreading Resistance Method'
J. Electrochem. Soc., 123, 1751-1754 (1976)
Comment : R. 150 keV 11B -> Si P/N Junction
1976-Kudo
1049

1976
Lanford, W. A.   Trautvetter, H. P.   Ziegler, J. F.   Keller, J.
'A New Precision Technique for Measuring the Concentration Versus Depth of Hydrogen in Solids'
Appl. Phys. Letters, 28, 566-68 (1976)
Comment : R, dR. 7.5 keV H -> Si (Cryst.)
1976-Lanf
0824

1976
Ligeon, E.   Guivarc'H, A.
'Hydrogen Implantation in Silicon Between 1.5 - 60 keV.'
Rad. Effects, 27, 129-37 (1976)
Comment : S,R,dR. 1.5-60 keV H -> Si. S. 1.5-60 keV H, 2.0 MeV 11B -> Si
1976-Lige
0817

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1976	Marcyk, G. T. Streetman, B. G. **'Boron Impurity Profile Tailoring in Silicon by Ion Implantation Measurement by Glow Discharge Optical Spectroscopy'** ***J. Electrochem. Soc., 123, 1388-1391 (1976)***	**1976-Marc** 1016
Comment :	*R. 50-250 keV B -> Si*	
1976	Matsumura, H. Furukawa, S. **'Simple Formulation for Energy Straggling of Helium in Silicon'** ***Rad. Effects, 27, 245-46 (1976)***	**1976-Mats** 0890
Comment :	*dS. 1-2 MeV He -> Si*	
1976	Mende, G. Kuster, G. **'Die Abtragung Dunner Schichten von P- und B-Implantierten Silizium Mit Hilfe der Anodischen Oxydation'** ***Thin Solid Films, 35, 215-220 (1976)***	**1976-Mend** 0875
Comment :	*R, dR. 30 keV H -> Si*	
1976	Natsuaki, N. Tamura, M. Tokuyama, T. **'Low Energy and High Dose Phosphorus Ion Implantation into Silicon through SiO2 Film'** ***Jap. J. Appl. Phys., 15, 2427-2432 (1976)***	**1976-Nats** 1050
Comment :	*R. 3 keV P -> Si, SiO2*	
1976	Neuwirth, W. Pietsch, W. Hauser, U. **'Stopping Cross Sections of Elements with Z=2 to 87 for Li Ions with Energies Between 80 keV and 840 keV'** ***Physics Data, Erstes Phsikalisches Institut, Univ. Zu Koln, Germany (1976)***	**1976-Neuw** 1178
Comment :	*S. 80-840 keV Li -> (2 <= Z2 <= 87)*	
1976	Oetzmann, H. Feuerstein, A. Grahmann, H. Kalbitzer, S. **'Range Parameters of Heavy Ions in Silicon and Germanium with Released Energies from 0.01 < epsilon < 10'** ***Meyer, G. Linker and F. Kappeler (Ed.):Ion Beam Surface Layer Analysis, Plenum, N. Y., P. 245-54 (1976)***	**1976-Oetz** 0845
Comment :	*R, dR. (1-40 keV) Al, Sb, As, Ge, Au, Bi -> Si, Ge*	
1976	Ryssel, H. Kranz, H. Biersack, J. Muller, K. Henkelmann, R. A. **'Boron Profiles and Diffusion Behavior in SiO2-Si Structures'** ***Ion Implantation in Semiconductors, Ed. by F. Chernow, J. A. Borders, D. K. Brice, 727-734 (1976)***	**1976-Ryss** 1015
Comment :	*R. 30-150 keV B -> Si, SiO2*	
1976	Santry, D. C. Werner, R. D. **'Range of Heavy Ions Implanted into Solids as Measured by He Ion Backscattering'** ***Nucl. Inst. Methods, 139, 135-146 (1976)***	**1976-Sant** 1053
Comment :	*R, dR. 0.12-2.0 MeV Bi, Xe, Kr -> C, Al, Si*	

1976
Schimmerling, W. Vosburgh, K. G. Todd, P. W. Appleby, A.
'Apparatus and Dosimetry for High-Energy Heavy-Ion-Beam Irradiations'
Rad. Res., 65, 389-413 (1976)
Comment : R. 3.9, 7.2 GeV N, 5.7 GeV Ne -> Si
1976-Schi
1268

1976
Wilken, B. Fritz, T. A.
'Energy Distribution Functions of Low Energy Ions in Silicon Absorbers Measured for Large Relative Energy Losses'
Nucl. Inst. Methods, 138, 331-343 (1976)
Comment : dS. 300 keV-1.5 MeV H, 3He -> Si
1976-Wilk
1051

1976
Williams, J. S.
'The Application of Low Angle Rutherford Backscattering to Surface Layer Analysis'
Meyer, G. Linker and F. Kappeler (Ed.):Ion Beam Surface Layer Analysis, Plenum, N. Y., P. 223-34 (1976
Comment : R, dR. 5 keV Cr -> Ge, 20 keV Pb -> Si
1976-Will
0852

1977
Blamires, N. G. Smith, B. J.
'The Range of Doubly Charged Boron Ions'
J. Phys. D, 10, 799-804 (1977)
Comment : R. 80, 360 keV B -> Si, SiO2
1977-Blam
1078

1977
Bogh, E. Hogild, P. Stensgaard, I.
'Spatial Distribution of Defects in Ion Bombarded Silicon and Germanium'
Rad. Effects, 7, 115-121 (1977)
Comment : R. 10-400 keV P, Sb -> Si, Ge
1977-Bogh
0968

1977
Cembali, F. Zignani, F.
'Determination of Random and Aligned Stopping Powers for 80-300 keV Protons in Silicon by Backscattering Measurements'
Rad. Effects, 31, 169-173 (1977)
Comment : S. 80-300 keV H -> Si Single Crystal ([110], [100], [111], and Random)
1977-Cemb
1033

1977
Christodoulides, C. E. Grant, W. A. Williams, J. S.
'Rutherford Backscattering Analysis of Ion-Implanted, Thermally Oxidized Silicon'
J. Electrochem. Soc., 124, 1651-1653 (1977)
Comment : R. 20 keV Dy, Pb, Xe -> Si (With SiO2)
1977-Chri
1054

1977
Christodoulides, C. E. Grant, W. A. Williams, J. S.
'Lattice Location of Lead Implanted into Silicon at Room Temperature'
Appl. Phys., 13, 391-393 (1977)
Comment : R, dR. 20 keV Pb -> Si [111]
1977-Chri2
1061

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1977	Chu, W. K. Kastl, R. H. Lever, R. F. Mader, S. Masters, B. J. **'Distribution of Irradiation Damage in Silicon Bombarded with Hydrogen'** ***Phys. Rev. B, 16, 3851-3859 (1977)*** *Comment : R. 50-250 keV H -> Si [001]. Ranges From Profiling Of Lattice Damage.*	**1977-Chu** 1037
1977	Das, G. **'Analysis of Defects in P-Implanted Silicon'** ***Electrochem. Soc. Extended Abstracts, 190, May (1977)*** *Comment : R. 50 keV P -> Si*	**1977-Das** 1060
1977	Grigor'eva, G. M. Kolodin, L. G. kreinin, L. B. Mukashev, B. N. Nusupov, K. Kh. **'Radiation Defects in p-type Silicon Irradiated with 30 MeV Protons'** ***Sov. Phys. Semicond., 11 (11), 1278-1280 (1977)*** *Comment : R,dR. H (30 MeV) -> Si*	**1977-Grig** 2127
1977	Hirao, T. Inoue, K. Takayanagi, S. Yaegashi, Y. **'Depth Distribution of Knock-On Nitrogen in Si by Phosphorus Implantation through Si3N4 Films'** ***Appl. Phys. Letters, 31, 505-508 (1977)*** *Comment : R. 100-220 keV P, N -> Si*	**1977-Hira** 1027
1977	Holland, O. W. Appleton, B. R. **'Well-Channelled Ions with Greater-Than-Random Energy Loss Rates'** ***IEEE Proc. of 4th Intl. Conf. on Small Accelerators, Denton, Tex. (1977)*** *Comment : S. 1.0 MeV He -> Si <111>*	**1977-Holl** 1257
1977	Jarvis, O. N. Sherwood, A. C. Whitehead, C. Lucas, M. W. **'Stopping Power for Fast Channeled Alpha Particles in Silicon'** ***Phys. Rev. B, 16, 3880-3886 (1977)*** *Comment : S. 160 MeV He -> Si ([110], [111], And Random)*	**1977-Jarv** 1038
1977	Lecrosnier, D. Paugam, J. Gallou, J. **'Channeling of Boron Ions into Silicon'** ***Appl. Phys. Letters, 30, 323-25, (1977)*** *Comment : R, dR. 50 keV-1.8 MeV B -> Si*	**1977-Lecr** 0943
1977	Nagy, A. Z. Bogancs, J. Gyulai, J. Csoke, A. Nazarov, V. **'Determination of Boron Range Distribution in Ion-Implanted Silicon by the 10B(n,alpha)7Li Reaction'** ***J. Radioanal. Chem., 38, 19-27 (1977)*** *Comment : R, dR. 20-80 keV B -> Si*	**1977-Nagy** 1094
1977	Nojima, S. Yamazaki, H. Harada, H. Fujimoto, M. **'Annealing Characteristics of Arsenic-Implanted Silicon'** ***Jap. J. Appl. Phys., 16, 193-194 (1977)*** *Comment : R. 220 keV As -> Si (With Anneal)*	**1977-Noji** 1028

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1977	Ricco, R. P. Goldstein, J. I. Mccallum, J. G. **'The Diffusion of Implanted Boron in Silicon'** ***J. Electrochem. Soc., 124, 276-279 (1977)*** *Comment : R. 300 keV B -> Si (Diffusion At 1000 Deg C)*	**1977-Ricc** 1055
1977	Ryssel, H. Kranz, H. Muller, K. Henkelmann, R. A. Biersack, J. **'Comparison of Range and Range Straggling of Implanted 10B and 11B in Silicon'** ***Appl. Phys. Letters, 30, 399-401, (1977)*** *Comment : R, dR. 20-200 keV 10B, 11B -> Si*	**1977-Ryss** 0942
1977	Shimizu, R. Kang, S. T. Koshikawa, T. Ogata, H. Kanayama, K. **'Monte Carlo Simulation of Depth and Lateral Profiles of Boron Atoms Implanted in Polycrystalline Silicon'** ***J. Appl. Phys., 48, 1745-47 (1977)*** *Comment : R, dR. 150 keV B -> Si.*	**1977-Shim** 0936
1977	Thompson, D. A. Robinson, J. E. Walker, R. S. **'Inelastic Stopping of Medium Energy Light Ions in Silicon'** ***Rad. Effects, 32, 169-175 (1977)*** *Comment : dS,R,dR. 10-80 keV H, He, Li, B, C, N, O, Ne -> Si*	**1977-Thom** 1076
1977	Tsudamoto, K. Akasaka, Y. Horie, K. **'Arsenic Implantation into Polycrystalline Silicon and Diffusion to Silicon Substrate'** ***J. Appl. Phys., 48, 1815-1821 (1977)*** *Comment : R, dR. 60-350 keV As -> Si*	**1977-Tsud** 1056
1978	Battaglin, G. DellaMea, G. Drigo, A. V. Foti, G. Bentini, G. G. **'Two-Stage Laser Annealing of Lattice Disorder in Phosphorus Implanted Silicon'** ***Phys. Stat. Sol. A, 49, 347-352 (1978)*** *Comment : R, dR. 100 keV 31P -> Si*	**1978-Batt** 1241
1978	Bottiger, J. Jensen, P. S. Littmark, U. **'Depth Profiles of 3He Ions Implanted into Solids at Energies Between 20 and 60 keV'** ***J. Appl. Phys., 49, 965-970 (1978)*** *Comment : R, dR. 20-60 keV 3He -> C, Al, Si, V, Ni, Zr*	**1978-Bott2** 1091
1978	Campisano, S. U. Ciavola, G. Vitali, G. **'Channeling and Rheed Analyses of Pb-Implantation in Silicon'** ***Appl. Phys., 15, 233-237 (1978)*** *Comment : R. 40 keV Pb -> Si*	**1978-Camp** 1126

1978
Carnera, A. Della Mea, G. Drigo, A. V. Lo Russo, S. Mazzoldi, P.
'Channeled and Random Proton Stopping Power in Si in the 300-1000 keV Energy Range'
Phys. Rev. B, 17, 3492 (1978)
Comment : *S. H (40-900 keV) -> Si. Channeled and Random stopping powers.*
1978-Carn
1631

1978
Cembali, F. Dori, L. Galloni, R. Servidori, M. Zignani, F.
'Radiation Damage in Silicon Produced by Phosphorus Implantation: Random and Aligned Implants'
Rad. Effects, 36, 111-117 (1978)
Comment : *R. 200 keV P -> Si*
1978-Cemb
1109

1978
Christodoulides, C. E.
'Impurity Redistribution in Pb Implanted and Annealed Silicon'
Phys. Letters, 67A, 83-86 (1978)
Comment : *R, dR. 80-180 keV Pb -> Si*
1978-Chri
1180

1978
Christodoulides, C. E. Carter, G. Williams, J. S.
'Implant Redistribution in High-Dose Ion Implanted and Annealed Silicon'
Intl. Conf. Ion Beam Modification of Materials, Budapest -a (1978)
Comment : *R, dR. 20-80 keV As, Pb -> Si*
1978-Chri2
1179

1978
Chu, W. K. Kastl, R. H. Lever, R. F. Mader, S. Masters, B. J.
'Damage Profiling for Hydrogen Implanted in Silicon'
Phys. Rev. B, (1978)
Comment : *R, dR. 50 - 250 keV H -> Si. (Damage Dist. Of H Implantation)*
1978-Chu 2
0932

1978
Combasson, J. L. Farmery, B. W. McCulloch, D. Neilson, G. W. Thompson, M. W.
'Heavy Ion Ranges in Aluminum and Silicon'
Rad. Effects, 36, 149-156 (1978)
Comment : *R, dR. 20-250 keV Cs, La, Pr, Eu, Tb, Dy, Ho, Er, Lu, Hf, Pt, Au, Tl, Pb, Bi -> Al; Sm, Eu, Gd, Tb, Dy -> Si*
1978-Comb
1166

1978
Cullis, A. G. Seidel, T. E. Meek, R. L.
'Comparative Study of Annealed Neon-, Argon-, and Krypton- Ion Implantation Damage in Silicon'
J. Appl. Phys., 49, 5188-5198 (1978)
Comment : *R, dR. 80 keV 20Ne, 150 keV 40Ar, 300 keV 84Kr -> Si*
1978-Cull
1217

1978
Furuya, T. Nishi, H. Inada, T. Sakurai, T.
'Channeled-Ion Implantation of Group-III and Group-V Ions into Silicon'
J. Appl. Phys., 49, 3918-3921 (1978).
Comment : *R, dR. 100-300 keV B, P, As, Al, Ga -> Si [111], [110], Random*
1978-Furu
1214

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1978	Gill, S. S. Wilson, I. H. **'Rutherford Backscattering Analysis of Oxide Layers Formed by Ion Implantation into Single-Crystal Silicon'** ***Thin Solid Films, 55, 435-448 (1978)*** Comment : *R, dR. 40, 60 keV O -> Si*	**1978-Gill** 1245
1978	Jarvis, O. N. Sherwood, A. C. Whitehead, C. Lucas, M. W. **'Channeling of Fast Protons, Deuterons and Alpha Particles'** ***Preprint (1978)*** Comment : *S, R, dR. 160 keV He, 81.5 keV D, 158.5 keV H -> Si*	**1978-Jarv** 1148
1978	Kappert, H. F. Heidemann, K. F. Grabe, B. te Kaat, E. **'Range and Damage Profiling after Heavy Ion Implantation in the MeV Region'** ***Phys. Stat. Sol. A, 47, 751 (1978)*** Comment : *R,dR. O, Si (2 MeV) -> Si*	**1978-Kapp** 2126
1978	Langley, R. A. Brice, D. K. **'Energy Straggling of Protons in Be, C, Al, Si'** ***Phys. Rev. B, 18, 4673 (1978)*** Comment : *dS. (.5-2.5 MeV) H -> Be, C, Al, Si*	**1978-Lang3** 1149
1978	Marcovich, A. Bahir, G. Bernstein, T. Kalish, R. **'A Method for Measuring Stopping Powers of Channeled Ions: Boron in Si'** ***Rad. Effects, 39, 65-70 (1978)*** Comment : *S, dS. 350-400 keV B -> Si*	**1978-Marc** 1203
1978	Mittenbacher, J. Gartner, K. **'Proton Ranges in Silicon and in Si-SiO2 Double Layers'** ***Intl. Conf. Ion Beam Modification of Materials, Budapest -c (1978)*** Comment : *R. 40-700 keV H -> Si, SiO2*	**1978-Mitt** 1175
1978	Miyao, M. Tamura, M. Tokuyama, T. **'Selective Annealing of Ion-Implanted Amorphous Layers by Nd3+-Yag Laser Irradiation'** ***Appl. Phys. Letters, 33, 828-830 (1978)*** Comment : *R, dR. 50 keV P -> Si*	**1978-Miya** 1210
1978	Miyao, M. Yoshihiro, N. Tokuyama, T. Mitsuishi, T. **'Correlation Between Lattice Damage and Electrical Activation of Phosphorus-Implanted Silicon'** ***J. Appl. Phys., 49, 2573-2575 (1978)*** Comment : *R. 50 keV P -> Si*	**1978-Miya2** 1114
1978	Nakamura, K. Kamoshida, M. **'Implanted As Redistribution During Annealing in Oxidizing Ambient'** ***J. Electrochem. Soc., 125, 1518-1521 (1978)*** Comment : *R, dR. 40-120 keV As -> Si*	**1978-Naka** 1339

Citations for Target : **Si**

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1978	Nashiyama, I. **'Depth Profile Analysis of Proton Damage by Channeling'** ***Phys. Rev. B, 17, 104-110 (1978)*** *Comment : R. 0.8-1.2 MeV H3 -> Si. Ranges Of Lattice Damage.*	**1978-Nash** 1105
1978	Nishi, H. Sakurai, T. Furuya, T. **'Electrical Activation of Implanted Arsenic in Silicon During Low Temperature Anneal'** ***J. Electrochem. Soc., 125, 461-466 (1978)*** *Comment : R. 100 keV As -> Si*	**1978-Nish** 1120
1978	Oetzmann, H. Kalbitzer, S. **'4He Stopping Power Measurements by using Ion Implantation and Backscattering Techniques'** ***Intl. Conf. Ion Beam Modification of Materials, Budapest -d (1978)*** *Comment : S. 0.15-1 MeV He -> C, Ge, Si*	**1978-Oetz** 1134
1978	Ohmura, Y. Inoue, T. Yamamoto, Y. **'Spatially Varied Activation of Ion-Implanted as During the Regrowth of Amorphous Layers in Si'** ***J. Appl. Phys., 49, 3597-3599 (1978)*** *Comment : R. 100 keV As -> Si*	**1978-Ohmu** 1113
1978	Onheiser, P. Zaruba, I. Cervena, J. Hnatowicz, V. Kosina, Z. **'A Study of Boron Ion Implanted Profiles in Silicon from 10B(n,alpha)7Li Reaction Product Spectra'** ***Intl. Conf. Ion Beam Modification of Materials, Budapest -b (1978)*** *Comment : R, dR. 50-400 keV B -> Si*	**1978-Onhe** 1184
1978	Roosendaal, H. E. Kool, W. H. Saris, F. W. **'Production and Beam Annealing of Damage in Carbon Implanted Si'** ***Rad. Effects, 36, 35-40 (1978)*** *Comment : R. 25, 50, 70 keV C -> Si*	**1978-Roos** 1111
1978	Rosendahl, E. W. Monkediek, J. **'Measurement of the Energy Loss of Non-Channeled Alpha-Particles in Transmission and Interpretation with the Aid of an Averaged Continuum Potential'** ***Z. Physik A, 285, 33-36 (1978)*** *Comment : S. 8.78 MeV He -> Si*	**1978-Rose** 1125
1978	Switkowski, Z. E. Overley, W. K. Wu, S. C. Barnes, C. A. Roth, J. **'Depth Profiling of Implanted Neon with Resonant Nuclear Reactions'** ***J. Nucl. Mater., (1978)*** *Comment : R, dR. 100 keV Ne -> Ta, 30, 40, 50, 80, 100, 160 keV Ne -> Si*	**1978-Swit** 1093

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1978	Tsai, M. Y. Streetman, B. G. Williams, P. Evans, C. A. **'Anomalous Migration of Fluorine and Electrical Activation of Boron in BF2-Implanted Silicon'** ***Appl. Phys. Letters, 32, 144-147 (1978)*** *Comment : R. 150 keV BF2+ -> Si*	**1978-Tsai** 1098
1978	White, C. W. Christie, W. H. Appleton, B. R. Wilson, S. R. Pronko, P. P. **'Redistribution of Dopants in Ion-Implanted Silicon by Pulsed-Laser Annealing'** ***Appl. Phys. Letters, 33, 662-664 (1978)*** *Comment : R, dR. 35 keV 11B, 80 keV 31P, 100 keV 75As -> Si*	**1978-Whit** 1209
1978	Wilson, R. G. Dunlap, H. L. Jamba, D. M. **'Angular Sensitivity of Controlled Implanted Doping Profiles'** ***NBS Special Publication 400-49 (1978).*** *Comment : R, dR. 20 - 150 keV B -> Si*	**1978-Wils2** 1146
1978	Yokota, K. Tamura, S. Gamo, K. Namba, S. Masuda, K. **'Ion-Implanted Arsenic Profiles in GaAs Encapsulated by SiO2 and Si3N4'** ***Jap. J. Appl. Phys., 17, 1881-1882 (1978)*** *Comment : R, dR. 150 keV As -> Si*	**1978-Yoko** 1338
1978	Young, R. T. White, C. W. Clark, G. J. Narayan, J. Christie, W. H. **'Laser Annealing of Boron-Implanted Silicon'** ***Appl. Phys. Letters, 32, 139-141 (1978)*** *Comment : R. 35 keV B -> Si (Compares Laser And Conventional Annealing)*	**1978-Youn** 1097
1978	Ziegler, J. F. Wu, C. P. Williams, P. White, C. W. Terreault, B. **'Profiling Hydrogen in Materials using Ion Beams'** ***Nucl. Inst. Methods, 149, 19-39 (1978)*** *Comment : R. 40 keV H, 31 keV D -> Si. Multiple-Technique. A Definitive Effort.*	**1978-Zieg** 0960
1979	Ahmed, N. A. G. Christodoulides, C. E. Carter, G. **'The Depth Distribution of Disorder Produced by Room Temperature 30 keV Ar+ and Cl+ Ion Irradiation of Silicon'** ***Phys. Letters, 69A, 431-435 (1979)*** *Comment : R, dR. 30 keV Ar, Cl -> Si*	**1979-Ahme** 1227
1979	Bayerl, P. Ryssel, H. Ramin, M. **'High Energy Implantation of Buried Insulating Layers'** ***Preprint (1979) 4*** *Comment : R, dR. 0.05-5.0 MeV N -> Si*	**1979-Baye** 1176
1979	Bister, M. Hautala, M. Jantti, M. **'Comparison of Experimental and Theoretical Ranges of Heavy Ions in the Low Energy Region'** ***Rad. Effects, 42, 201-208, (1979)*** *Comment : R, dR. 20-190 keV Eu, Cs, La, Au, Al -> Si, Al, Ti, Ta*	**1979-Bist** 1318

1979 Blood, P. Brown, W. L. Miller, G. L. **1979-Bloo** 1137

'Incorporation of Implanted In and Sb in Silicon During Amorphous Layer Regrowth'

J. Appl. Phys., 50, 173-182 (1979)

Comment : R, dR. 100, 340 keV In -> Si, 240 keV Sb -> Si

1979 Comas, J. Wilson, R. G. **1979-Coma** 1145

'Channeling and Random Equivalent Depth Distributions of 150 keV Li, Be, and B Implanted in Si'

Preprint (1979) 2

Comment : S, R, dR. 150 keV Li, Be, B -> Si

1979 Doyle, B. L. Peercy, P. S. **1979-Doyl** 1135

'Technique for Profiling 1H with 2.5 MeV van de Graaff Accelerators.'

Appl. Phys. Letters, 34, 811-813 (1979)

Comment : R. 1-3 MeV H -> Si3N4, Si

1979 Greenwald, A. C. Kirkpatrick, A. R. Little, R. G. Minnucci, J. A. **1979-Gree** 1220

'Pulsed-Electron-Beam Annealing of Ion-Implantation Damage'

J. Appl. Phys., 50, 783-787 (1979)

Comment : R, dR. 10 keV P -> Si [111]

1979 Hirao, T. Fuse, G. Inoue, K. Takayanagi, S. Yaegashi, Y. **1979-Hira** 1380

'The Effects of the Recoil-Implanted Oxygen in Si on the Electrical Activation of As afterThrough-Oxide Implantation'

J. Appl. Phys., 50, 5251-5256 (1979)

Comment : R, dR. 180 keV As -> Si

1979 Hirao, T. Inoue, K. Takayanagi, S. Yaegashi, Y. **1979-Hira2** 1141

'The Concentration Profiles of Projectiles and Recoiled Nitrogen in Si after Ion Implantation through Si3N4 Films'

J. Appl. Phys., 50, 193-201 (1979)

Comment : R, dR. 160 keV P -> Si, 355 keV As -> Si, 50 keV B -> Si, 200 keV Ar -> Si

1979 Hirao, T. Inoue, K. Yaegashi, Y. Takayanagi, S. **1979-Hira3** 1213

'The Concentration Profiles of Phosphorus, Arsenic and Recoiled Oxygen Atoms in Si by Ion Implantation into SiO2-Si'

Jap. J. Appl. Phys., 18, 647-656 (1979)

Comment : R, dR. 70-350 keV P, 180 keV As -> Si Through SiO2

1979 Hubler, G. K. Malmberg, P. R. IiiSmith, T. P. **1979-Hubl** 1303

'Refractive Index Profiles and Range Distributions of Silicon Implanted with High-Energy Nitrogen'

J. Appl. Phys., 50, 7147-7155 (1979)

Comment : R, dR. 0.67-3.17 MeV N -> Si

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1979	Hubler, G. K. Waddell, C. N. Spitzer, W. G. Fredrickson, J. E. Prussin, S. **'High-Fluence Implantations of Silicon: Layer Thickness and Refractive Indices'** ***J. Appl. Phys., 50, 3294-3303 (1979)*** *Comment : R, dR. 0.20-2.7 MeV P, 0.30 MeV Si -> Si*	**1979-Hubl2** 1226
1979	Inoue, K. Hirao, T. Yaegashi, Y. Takayanagi, S. **'Asymmetrical Profiles of Ion Implanted Phosphorus in Silicon'** ***Jap. J. Appl. Phys., 18, 367-372 (1979)*** *Comment : R, dR. 150-300 keV P -> Si*	**1979-Inou** 1211
1979	Jarvis, O. N. Sherwood, A. C. Whitehead, C. Lucas, M. W. **'Channeling of Fast Protons, Deuterons, and Alpha Particles'** ***Phys. Rev. B, 19, 5559-5577 (1979)*** *Comment : S, R, dR. 160 keV He, 81.5 keV D, 158.5 keV H -> Si*	**1979-Jarv** 1199
1979	Kappert, H. F. Sixt, G. Schwuttke, G. H. **'Minority Carrier Lifetime in Silicon afterAr+ and Si+ Implantation'** ***Phys. Stat. Sol. A, 52, 463-474 (1979)*** *Comment : R, dR. 200 keV Ar, 80 keV Si -> Si*	**1979-Kapp** 1235
1979	Krynicki, J. Bourgoin, J. C. **'Defect Annealing in Phosphorus Implanted Silicon: A D.L.T.S. Experiment on Phosphorus Implants.'** ***Appl. Phys., 18, 275-278 (1979)*** *Comment : R, dR. 130 keV P -> Si*	**1979-Kryn** 1249
1979	Lukac, P. Jesenak, V. **'Distribution of Ion-Bombardment Implanted 85Kr in Si, Cu, and SiO2'** ***Phys. Stat. Sol. A, 55, 647-652 (1979)*** *Comment : R, dR. 5-50 keV Kr -> Si, Cu, SiO2*	**1979-Luka** 1344
1979	Magee, C. W. **'Depth Profilling of N-Type Dopants in Si and GaAs using Cs+ Bombardment Negative Secondary Ion Mass Spectrometry in Ultrahigh Vacuum'** ***J. Electrochem. Soc., 126, 660-663 (1979)*** *Comment : R, dR. 15 keV H, 80 keV P, 200 keV As -> Si; 200 keV Si, 250 keV S -> GaAs*	**1979-Mage** 1223
1979	Miyao, M. Yoshihiro, N. Tokuyama, T. Mitsuishi, T. **'Damage-Dependent Electrical Activation of Ion-Implanted Silicon. I. Experiments on Phosphorus Implants.'** ***J. Appl. Phys., 50, 223-230 (1979)*** *Comment : R, dR.50 keV P -> Si*	**1979-Miya** 1219
1979	Pham, M. T. **'A Very Simple Method for Profiling the Ion-Implanted Si-Surface'** ***Phys. Stat. Sol. A, 49, 261-265 (1979)*** *Comment : R. 30 keV Si, P, B, Ar, As; 12.2 keV In -> Si*	**1979-Pham** 1238

1979 Sakurai, T. Kawata, H. Sato, T. Hisatsugu, T. Hashimoto, H. **1979-Saku** 1138

'Lateral Spread of P+ Ions Implanted in Silicon through the SiO2 Mask Window'

J. Appl. Phys., 50, 1287-1290 (1979)

Comment : *R, dR. 150 keV P -> Si*

1979 Santry, D. C. Werner, R. D. Westcott, O. M. **1979-Sant** 1197

'The Range of 120 keV Ions in Solids'

IEEE Trans. Nucl. Sci., Ns-26, 1331-1334 (1979)

Comment : *R, dR. 120 keV Mg, Al, P, S, Cl, K, Ar, Cr, Mn, Cu, Zn, Ga, As, Br, Kr, Rb, Ag, In, Sn, Sb, Te, I, Xe, Cs, Ba, Pr, Au, Hg, Tl, Pb, Bi -> Be, C, Al, Si*

1979 Santry, D. C. Werner, R. D. **1979-Sant3** 1350

'Thickness Measurements of Thin Foils using Alpha Particles from 148Gd and 241Am'

Nucl. Inst. Methods, 159, 523-527 (1979)

Comment : *S, dS. 3.138 MeV - 5.486 MeV He -> Be, C, Al, Si, Ni, Ag, Au*

1979 Stein, H. J. Peercy, P. S. **1979-Stei** 1140

'Controlled Hydrogenation of Amorphous Silicon at Low Temperatures'

Appl. Phys. Letters, 34, 604-606 (1979)

Comment : *R, dR. 20 keV H -> Si*

1979 Titov, A. I. Christodoulides, C. E. Carter, G. Nobes, M. J. **1979-Tito** 1206

'The Depth Distribution of Disorder Produced by Room Temperature 40 keV N+ Ion Irradiation of Silicon'

Rad. Effects, 41, 107-111 (1979)

Comment : *R, dR. 40 keV N -> Si*

1979 Tsai, M. Y. Day, D. S. Streetman, B. G. Williams, P. Evans, Jr. C. A. **1979-Tsai** 1218

'Recrystallization of Implanted Amorphous Silicon Layers. II. Migration of Fluorine in BF2+-Implanted Silicon.'

J. Appl. Phys., 50, 188-192 (1979)

Comment : *R, dR. 50-200 keV 28Si, 25-85 keV 11B, 150 keV BF2 -> Si*

1979 Tsai, M. Y. Streetman, B. G. **1979-Tsai2** 1142

'Recrystallization of Implanted Amorphous Silicon Layers. I. Electrical Properties of Silicon Implanted with BF2+ or Si+B.'

J. Appl. Phys., 50, 183-187 (1979)

Comment : *R, dR. 34-200 B, BF2, Si -> Si*

1979 Wada, Y. Hashimoto, N. **1979-Wada** 1293

'Anomalous Carrier Tail Generation Mechanism in BF2 Ion-Implanted Layers of Silicon'

J. Appl. Phys., 50, 6257-6261 (1979)

Comment : *R, dR. 178 keV BF2 Implanted Into Si (Carrier Profiles).*

1979
Wada, Y.   Hashimoto, N.
'Anomalous Carrier Profiles in BF2 Ion-Implanted Silicon'
J. Appl. Phys., 50, 5720-25 (1979)
Comment : R, dR. 40 keV B->Si.
1979-Wada2
1294

1979
White, C. W.   Christie, W. H.   Pronko, P. P.   Appleton, B. R.   Wilson, S. R.
'Dopant Profile Changes Induced by Pulsed Laser Annealing'
Rad. Effects, 47, 37-40 (1979)
Comment : R, dR. 35-150 keV B, P, As, Sb, Cu, Fe -> Si
1979-Whit
1321

1979
White, C. W.   Pronko, P. P.   Wilson, S. R.   Appleton, B. R.   Narayan, J.
'Effects of Pulsed Ruby-Laser Annealing on As and Sb Implanted Silicon'
J. Appl. Phys., 50, 3261-3273 (1979)
Comment : R, dR. 100 keV 75As, 121Sb -> Si
1979-Whit2
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1980
Bentini, G. G.   Galloni, R.   Nipoti, R.
'Multiscanning Electron Beam Annealing of Phosphorus-Implanted Silicon'
Appl. Phys. Letters, 36, 661-663 (1980)
Comment : R, dR. 200 keV H -> Si
1980-Bent
1334

1980
Bernhard, F.   Kerkow, H.   Kudella, F.
'Depth Profile Measurements of Copper in Silicon by Ion-Induced X-Ray Emmision'
Rad. Effects, 49, 107-112 (1980)
Comment : R, dR. 200 keV Cu -> Si
1980-Bern
1388

1980
Besenbacher, F.   Bottiger, J.   Laursen, T.   Loftager, P.   Moller, W.
'Z1-Oscillations in Low-Energy Heavy-Ion Ranges'
Nucl. Inst. Methods, 170, 183-188 (1980)
Comment : R, dR.   Atomic Numbers 18-92 (epsilon=.015) -> Si
1980-Bese2
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1980
Bister, M.   Keinonen, J.   Anttila, A.
'On Dissimilarities of Heavy Ion Ranges in Aluminum and Silicon'
Phys. Letters, A, (1980)
Comment : R, dR. 120 keV Pb -> Al, Si
1980-Bist
1360

1980
Bolster, R. N.   Singer, I. L.
'Surface Hardness and Abrasive Wear Resistance of Nitrogen-Implanted Silicon'
Appl. Phys. Letters, 36, 208-209 (1980)
Comment : R, dR. 100 keV H -> Si
1980-Bols
1333

1980
Brylowska, I.   Subotowicz, M.   Paprocki, K.   Derewiecki, H.
'Doping Profiles from the Capacity-Voltage (C-V) Characteristics of the [111] Si(P) Single Crystals Doped by the In+-Ion-Implantation'
Rad. Effects, 47, 163-166 (1980)
Comment : R, dR. 30-90 keV In -> Si
1980-Bryl
1343

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1980
Campisano, S. U. Baeri, P. Foti, G. Ciavola, G. Rimini, E.
'Impurity Redistribution During Laser Irradiation in Ion Implanted Silicon'
Rad. Effects, 48, 187-190 (1980)
Comment : R, dR. 400 keV As -> Si
1980-Camp2
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Christodoulides, C. E. Carter, G. Williams, J. S.
'Implant Redistribution in High-Dose Ion Implanted and Annealed Silicon'
Rad. Effects, 48, 87-90 (1980)
Comment : R, dR. 80 keV Pb -> Si
1980-Chri
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Chu, W. K. Kastl, R. H. Murley, P. C.
'Low-Energy Antimony Implantation in Silicon'
Rad. Effects, 47, 1-6 (1980)
Comment : R, dR. 5-60 keV Sb -> Si
1980-Chu
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1980
Demond, F. J. Kalbitzer, S. Mannsperger, H. Muller, G.
'Range Parameters of Protons in Silicon Implanted at Energies from 0.5 to 300 keV.'
Nucl. Inst. Methods, 168, 69-74 (1980)
Comment : R, dR. .5-300 keV H -> Si
1980-Demo
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Desalvo, A. Galloni, R. Rosa, R. Zignani, F.
'Experimental and Computer Analysis of P+-Ion Penetration Tails in a SiO2-Si Two Layer System'
J. Appl. Phys., 51, 1994-1997 (1980)
Comment : R, dR. 150-keV P -> Si
1980-Desa
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Gat, A. Gerzberg, L. Gibbons, J. F. Lietoila, A. Johnson, N. M.
'Annealing of Ion-Implanted Si using a Scanned CW Laser System'
Rad. Effects, 48, 195-202 (1980)
Comment : R, dR. 35 keV B -> Si
1980-Gat
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1980
Heibei, J. Voges, E.
'Refractive Index of Ion-Implanted Fused Silica'
Phys. Stat. Sol. B, 57, 609-618 (1980)
Comment : R, dR. 100 keV He, Ar -> Si
1980-Heib
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1980
Hirao, T. Fuse, G. Inoue, K. Takayanagi, S. Yaegashi, Y.
'Electrical Properties of Si Implanted with As through SiO2 Films'
J. Appl. Phys., 51, 262-268 (1980)
Comment : R, dR. 180 keV As -> Si
1980-Hira
1301

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1980	Hirao, T. Inoue, K. Fuse, G. Takayanagi, S. T. Yaegashi, Y. **'The Concentration Profiles of the Recoil Implanted Oxygen in Si afterIon Implantations into SiO2-Si Substrates'** ***Rad. Effects, 47, 95-98 (1980)*** *Comment : R, dR. 100-220 keV P, Ar, As -> Si*	**1980-Hira2** 1326
1980	Izmailov, Sh. Z. Sirotinin, E. I. Tulinov, A. F. **'Energy Loss of Protons in Si, Ge, and Mo'** ***Nucl. Inst. Methods, 168, 81-84 (1980)*** *Comment : S, dS. .1-1 MeV H -> Si, Ge, Mo*	**1980-Izma** 1342
1980	Josquin, W. J. M. J. **'The Oxidation Characteristics of Nitrogen-Implanted Silicon'** ***Rad. Effects, 47, 221-224, (1980)*** *Comment : R, dR. 250-800 keV H, H2, He, B, P -> Si*	**1980-Josq** 1331
1980	Kalbitzer, S. Oetzmann, H. **'Ranges and Range Theories'** ***Rad. Effects, 47, 57-72, (1980)*** *Comment : R, dR. .1-2 MeV Bi, Sb, As, Ge, P, Au, Cs, Eu, Gd Tb -> Si, Ge, C, Al*	**1980-Kalb** 1323
1980	Kappert, H. F. Heidemann, K. F. Eichholz, D. Tekaat, E. Rothemund, W. **'Range and Range Straggling of Oxygen Implanted into Silicon at Energies Between 2 and 20 MeV'** ***Appl. Phys., 21, 151-158 (1980)*** *Comment : R, dR. 2-20 MeV 0 -> Si*	**1980-Kapp** 1348
1980	Komarov, F. F. Kuryazov, V. D. Solovev, V. S. Shiryaev, S. Yu. **'Formation of Structure Defects and Behavior of Ion-Implanted Boron in Silicon Under Annealing in Various Ambients'** ***Phys. Stat. Sol. A, 58, 99-105 (1980)*** *Comment : R, dR. 100 keV B -> Si*	**1980-Koma** 1347
1980	Land, D. J. Simons, D. G. Brennan, J. G. Brown, M. D. **'Z2 and Energy Dependence of Range Distributions and Stopping Powers for Nitrogen Ions in Solids'** ***Phys. Rev. A, 22, 1, 68-75 (1980)*** *Comment : S,R, dR. N (800 keV) -> 24 Solids (C-Pb)*	**1980-Land3** 1453
1980	MaGee, C. W. Cohen, S. A. Voss, D. E. Brice, D. K. **'Depth Distributions of Low Energy Deuterium Implanted into Silicon as Determined by SIMS'** ***Nucl. Inst. Methods, 168, 383-387 (1980)*** *Comment : R, dR. D (0.1-5 keV) -> Si*	**1980-MaGe** 1529

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1980	Muller, K. Henkelmann, R. Jahnel, F. Ryssel, H. Haberger, K. **'The Application of the (n,alpha)-Method of Boron Depth Profiling and Channeling - Blocking Measurement in Semiconductor Materials'** ***Preprint (1980) 6*** *Comment : R, dR. 60-210 keV B -> Si, SiO2*	**1980-Mull** 1363
1980	Myers, D. R. Wilson, R. G. **'Alignment Effects on Implantation Profiles in Silicon'** ***Rad. Effects, 47, 91-94 (1980)*** *Comment : R, dR. 300 keV B -> Si*	**1980-Myer** 1325
1980	Oetzmann, H. Kalbitzer, S. **'He4-Stopping Power Measurements by using Ion Implantation and Backscattering Techniques'** ***Rad. Effects, 47, 73-80 (1980)*** *Comment : S, dS. 0-1E5 keV He -> C, Si, Ge*	**1980-Oetz** 1324
1980	Peercy, P. S. Stein, H. J. Ginley, D. S. **'Effect of Disorder on the Hydrogen Content in Si'** ***Appl. Phys. Letters, 36, 678-680 (1980)*** *Comment : R, dR. 150-300 keV H -> Si*	**1980-Peer** 1335
1980	Rimini, E. Chu, W. K. Baglin, J. E. E. Tan, T. Y. Hodgson, R. T. **'Laser Annealing of Silicon Implanted with Both Argon and Arsenic'** ***Appl. Phys. Letters, 37, 81-83 (1980)*** *Comment : R, dR. 30-40 keV As Ar -> Si*	**1980-Rimi** 1381
1980	Ryssel, H. Hoffman, K. Haberger, K. Prinke, G. Muller, K. **'High Concentration Effects of Ion Implanted Boron in Silicon'** ***IEEE Trans. Nucl. Sci., NS-26, 378-379 (1980)*** *Comment : R, dR. 120 keV B -> Si*	**1980-Ryss** 1391
1980	Santry, D. C. Werner, R. D. **'Stopping Power Values of Be, C, Al and Si for 4He Ions'** ***Nucl. Inst. Methods, 178, 523-530 (1980)*** *Comment : S. He (0.2-2.0 MeV) -> Be, C, Al, Si*	**1980-Sant2** 1407
1980	Schmitt, A. Schorer, G. **'Damage Anneal of Antimony/Phosphorus Double Implants in Silicon'** ***Appl. Phys., 22, 137-143 (1980)*** *Comment : R, dR. 200 keV Sb -> Si*	**1980-Schm** 1390
1980	Sofield, C. J. Cowern, N. E. B. Freeman, J. M. **'Charge-Exchange Effects in Energy-Loss Straggling'** ***Nucl. Inst. Methods, 170, 221-225 (1980)*** *Comment : R, dR. 0-50 MeV Atomic Numbers 1-16 -> Al*	**1980-Sofi** 1378

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1980	Sugiura, H. **'Silicon Molecular Beam Epitaxy with Antimony Ion Doping'** ***J. Appl. Phys., 51, 2630-2633 (1980)*** *Comment : R, dR. 130-1000 eV Sb -> Si*	**1980-Sugi** 1299
1980	Takai, M. Ryssel, H. Kranz, H. Bayerl, P. **'Photo- and Electroluminescence of Nitrogen Isoelectronic Traps in GaAs'** ***Rad. Effects, 47, 211-216 (1980)*** *Comment : R, dR. 25-130 keV Ni -> Si*	**1980-Taka** 1330
1980	Wang, K. L. **'Primary Defects in Low-Fluence Ion-Implanted Silicon'** ***Appl. Phys. Letters, 36, 48-50 (1980)*** *Comment : R, dR. 40 keV Ni -> Si*	**1980-Wang** 1332
1980	Wilson, R. G. Comas, J. **'Correlation of Atomic Distribution and Implantation Induced Damage Profiles in Be-Ion Implanted Si'** ***Rad. Effects, 47, 137-142 (1980)*** *Comment : R, dR. 300 keV Be -> Si*	**1980-Wils** 1327
1980	Wilson, R. G. Vasudev, P. K. Jamba, D. M. Evans, C. A. **'Chromium Concentrations, Depth Distributions, and Diffusion Coefficient in Bulk and Epitaxial GaAs and in Si'** ***Appl. Phys. Letters, 36, 215-218 (1980)*** *Comment : R ,dR. 200 keV Cr -> Si*	**1980-Wils2** 1370
1981	Kuhrt, E. Lenkeit, K. Taubner, F. **'Measurements of the Stopping Power of 40-300 keV Protons in Silicon'** ***Phys. Stat. Sol. A, 66, 131 (1981)*** *Comment : S. H (40-300 keV) -> Si*	**1981-Kuhr** 1694
1981	Nakata, J. Kajiyama, K. **'Novel Low Temperature (< 300C) Annealing of Amorphous Silicon by Scanned High Energy (2.5 MeV) Heavy Ion Beam'** ***Jap. J. Appl. Phys., 21 (suppl. 21-1), 211-216 (1981)*** *Comment : R. As (50-100 keV) -> Si*	**1981-Naka** 2145
1981	Nakata, J. Takahashi, M. Kajiyama, K. **'In-situ Self Ion Beam Annealing of Damage in Si during High Energy As Ion Implantation'** ***Jap. J. Appl. Phys., 20, 2211-2221 (1981)*** *Comment : R. As (0.5-2.56 MeV) -> Si*	**1981-Naka2** 2143
1981	Pearce, J. D. Hart, R. R. **'Stopping Power Measurements in the 20-150 keV Region using Thick Target Backscattering: H and He on C, Si and Au'** ***J. Appl. Phys., 52, 5056 (1981)*** *Comment : S. H, He (20-150 keV) -> C, Si, Au*	**1981-Pear** 1736

Citations for Target : **Si**

Pub. Year	*Authors, Title, Journal Citation and Comments*	Citation Numb
1981	Santry, D. C. Werner, R. D. **'Stopping Powers of C, Al, Si, Ti, Ni, Ag and Au for Deuterons'** ***Nucl. Inst. Methods, 188, 211 (1981)*** *Comment : S. D (0.2-2.0 MeV) -> C, Al, Si, Ti, Ni, Ag, Au*	**1981-Sant** 1756
1981	Santry, D. C. Werner, R. D. **'Stopping Power Values of C, Al, Si, Ni, Ag and Au for 3He Ions'** ***Nucl. Inst. Methods, 185, 517-521 (1981)*** *Comment : S. He3 (200-2000 keV) -> C, Al, Si, Ni, Ag, Au*	**1981-Sant2** 1449
1981	Takahashi, M. Nakata, J. Kajiyama, K. **'High Energy As Ion Implantation into Si - Arsenic Profiles and Electrical Activation Characteristics'** ***Jap. J. Appl. Phys., 2205-2209 (1981)*** *Comment : R. As (0.2-2.5 MeV) -> Si*	**1981-Taka** 2144
1982	Byrne, P. F. Cheung, N. W. Sadana, D. K. **'Megavolt Arsenic Implantation into Silicon'** ***Thin Sol. Films, 363-367 (1982)*** *Comment : R. As (11 MeV) -> Si*	**1982-Byrn** 2141
1982	Fahrner, W. R. Heidemann, K. Schottle, P. **'Results of Ion Implantation into Silicon in the 100 MeV Range'** ***Phys. Stat. Sol. A, 70, 463-472 (1982)*** *Comment : R, dR. O, B (56-65 MeV) -> Si*	**1982-Fahr** 1507
1982	Geissel, H. Laichter, Yl Schneider, W. F. W. Armbruster, P. **'Energy Loss and Energy Loss Straggling of Fast Heavy Ions in Matter'** ***Nucl. Inst. Methods, 194, 21-29 (1982)*** *Comment : S. Heavy Ions (18 - 92) at 0.5-10 MeV/amu -> 17 Solids and 5 Gases*	**1982-Geis** 1417
1982	Nakata, J. Kajiyama, K. **'Precise Profiles for Arsenic Implanted in Si and SiO2 over a Wide Implantation Energy Range (10 keV - 2.56 MeV)'** ***Jap. J. Appl. Phys., 21, 1363-1369 (1982)*** *Comment : R. As (10 keV - 2.56 MeV) -> Si, SiO2*	**1982-Naka** 2142
1982	Nakata, J. Kajiyama, K. **'Novel Low Temperature Recrystallization of Amorphous Silicon by High Energy Ion Beam'** ***Appl. Phys. Letters, 40, 686-688 (1982)*** *Comment : R. Kr, As (2.5 MeV) -> Si*	**1982-Naka2** 2146
1982	OConnor, D. J. **'Accurate RBS Determination of the Range Profile of Implanted Bismuth in Silicon'** ***Nucl. Inst. Methods, 196, 493-497 (1982)*** *Comment : R. Bi (26-120 keV) -> Si*	**1982-OCon** 2019

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1983	Byrne, P. F. Cheung, N. W. Sadana, D. K. Polla, D. L. **'Electrical Characteristics of Silicon Implanted with 11 MeV Arsenic'** ***Proc. Elec. Chem. Soc., 5/83, 589-594 (1983)*** *Comment : R. As (11 MeV) -> Si*	**1983-Byrn2** 2147
1983	Fink, D. Biersack. J. P. Stadele, M. Tjan, K. Cheng, V. K. **'Nitrogen Depth Profiling using the N(n,p)C Reaction'** ***Nucl. Inst. Methods, 218, 171-175 (1983)*** *Comment : R. N(1.5 MeV) -> Al, Si, Fe, Ni, Cu, Co, Ge,Zr, Nb, Mo, Sn, Pb*	**1983-Fink2** 2117
1983	Hancock, S. James, F. Movchet, J. Rancoita, P. G. Van Rossum, L. **'Energy Loss and Energy Straggling of Protons and Pions in the Momentum Range 0.7-115 GeV/c'** ***Phys. Rev. A, 28, 615*** *Comment : S,dS. H, pions (0.7-115 GeV/c) -> Si*	**1983-Hanc** 1659
1983	Malherbe, J. B. **'Projected Range and Straggling Measurements of Low Energy Nitrogen in Silicon'** ***Rad. Effects, 70, 261-274 (1983)*** *Comment : R, dR. N (0.25-2.5 keV) -> Si*	**1983-Malh** 1506
1983	Mannsperger, H. Kalbitzer, S. Demond, F. J. Damjantschitsch, H. **'Projection Factors of Low Energy Ion Ranges'** ***Nucl. Inst. Methods, 209/210, 49-55 (1983)*** *Comment : R. H, C, Na, Al, Si, Ar, Cr (.04<epsilon<1) -> Si, Ge*	**1983-Mann** 2199
1983	Wach, W. Wittmaack, K. **'Ranges of Low Energy Light Ions in Amorphous Silicon'** ***Phys. Rev. B, 27 (6), 3528-3537 (1983)*** *Comment : R, dR. Li, B, N, O, F, Na, Mg, Al ((1-20 keV) -> Si*	**1983-Wach** 1528
1984	Behar, M. Beirsack, J. P. Fichtner, P. F. P. Fink, D. Leite-Filho, C. V. **'Range and Range Straggling of 15-350 keV Ga in Amorphous Silicon'** ***Rad. Effects Letters, 85, 117-122(1984)*** *Comment : R, dR. Ga (15-350 keV) -> Si*	**1984-Beha** 1525
1984	Byrne, P. F. Cheung, N. M. Tam, S. Hu, C. Shih, Y. C. **'Megavolt Boron and Arsenic Implantation into Silicon'** ***Mat. Res. Soc. Sym., 27,253-258 (1984)*** *Comment : R, dR. B, As (4-11 MeV) -> Si*	**1984-Byrn** 1527
1984	Heidemann, K. F. Gruner, M. Kaat, E. **'Optical Characterization of Damage and Concentration Profiles in H Ion Implanted Amorphous Silicon'** ***Rad. Effects, 82, 103-131 (1984)*** *Comment : R, dR. H (190 keV) -> Si (Optical Characterization)*	**1984-Heid** 1519

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1984	Rybka, V. Hnatowicz, V. Kvitek, J. Vacik, J. Schmidt, B. **'Determination of the Range Profiles of Boron Implanted into Si and SiO2'** ***Phys. Stat. Sol. A, 83, 165-171 (1984)*** *Comment : R, dR. B (30-200 keV) -> Si, SiO2*	**1984-Rybk** 1446
1984	Santry, D. C. Werner, R. D. **'Stopping Powers of C, Al, Si, Ti, Ni, Ag, Au and Mylar using Radioactive Alpha Sources'** ***Nucl. Inst. Methods, B1, 13 (1984)*** *Comment : S. He (2-7 MeV) -> > C, Al, Si, Ti, Ni, Ag, Au, Mylar*	**1984-Sant** 1757
1984	Santry, D. C. Werner, R. D. **'Stopping Powers of C, Al, Si, Ti, Ni, Ag and Au for Li-7 Ions'** ***Nucl. Inst. Methods, B5, 449 (1984)*** *Comment : S. Li (0.2-1.8 MeV) -> > C, Al, Si, Ni, Ag, Au*	**1984-Sant2** 1758
1984	Sirotinin, E. I. Tulinov, A. F. Khodyrev, V. A. Mizgulin, V. N. **'Proton Energy Loss in Solids'** ***Nucl. Inst. Methods, B4, 337 (1984) -1*** *Comment : S. H (0.1-6.0 MeV) -> Al, Si, Sc, V, Cu, Zn, Ga, Ge, Y, Zr, Nb, Mo, Ag, Cd, In, Sn, La, Sm, Gd, Yb, Hf, Ta, W, Pt, Au, Pb*	**1984-Siro** 1770
1984	Vander Vorst, W. Maes, H. E. de Keersmaecker, R. F. **'Secondary Ion Mass Spectrometry: Depth Profiling of Shallow As Implants in Silicon and SiO2'** ***J. Appl. Phys., 56, 1425-1433 (1984)*** *Comment : R. As (4-40 keV) -> Si*	**1984-Vand** 2014
1984	Wilson, R. G. Jamba, D. M. Hapkins, C. G. Norberg, J. C. **'Unannealed and Annealed Depth Distribution of Mercury Implanted into Silicon'** ***J. Appl. Phys., 55 (2), 327-330 (1984)*** *Comment : R, dR. Hg (300-900 keV) -> Si*	**1984-Wils** 1505
1985	Behar, M. Fichtner, P. F. Olivieri, C. A. DeSouza, J. P. Zawislak, F. C. **'Range Profiles of Implanted Bi and Au in Amorphous Silicon'** ***Nucl. Inst. Methods, B6, 453-458 (1985)*** *Comment : R, dR. Bi, Au (10-390 keV) -> Si*	**1985-Beha** 1508
1985	Behar, M. Fichtner, P. F. Olivieri, C. A. DeSouza, J. P. Zawislak, F. C. **'Range Profiles of 10-380 keV Sn and Cs into Amorphous Silicon'** ***Rad. Effects, 90, 103-110 (1985)*** *Comment : R, dR. Sn, Cs (10-380 keV) -> Si*	**1985-Beha2** 1509

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1985	Gehrmann, P. Lenkeit, K. Stolle, R. **'Measurement of Proton Channeling Energy Losses in Silicon in the Intermedicate Energy Region'** ***Phys. Stat. Sol. B, 131, 519 (1985)*** *Comment : S. H (40-350 keV) -> Si. Channeled stopping powers.*	**1985-Gehr** 1963
1985	Hautala, M. Keinonen, J. Whitlow, H. J. Tikkanen, P. Uhrmacher, M. **'Range Profiles of 25-250 keV Hydrogen in Silicon'** ***Phys. Letters, 109A, 344-346 (1985)*** *Comment : R, dR. H (25-250 keV) -> Si*	**1985-Haut** 1534
1985	Ingrahm, D. C. Baker, J. A. Walsh, D. A. **'Range Distributions of MeV Implants in Silicon'** ***Nucl. Inst. Methods, B7/8, 361-365 (1985)*** *Comment : R, dR. B, P, Sb (0.4-6 MeV) -> Si*	**1985-Ingr** 1526
1985	Jeynes, C. Kimber, A. C. **'High Accuracy Data for RBS: Measurements of Range and Straggling of 60-400 keV As into Si'** ***J. Phys. D: Appl. Phys., 18, L93-97 (1985)*** *Comment : R, dR. As (60-400 keV) -> Si*	**1985-Jeyn** 1531
1985	Land, D. J. Simons, D. G. Brennan, J. G. Glass, G. A. **'Range Distributions and Electronic Stopping Power of Nitrogen Ions in Solids'** ***Nucl. Inst. Methods, B10/11, 234-236 (1985)*** *Comment : S,R, dR. N (800 keV) -> 24 Solids (C-Pb)*	**1985-Land** 1454
1986	Bimbot, R. Gauvin, H. Orliange, I. **'Stopping Powers of Solids for Ar and Ca Ions at Intermediate Energies (20-80 MeV/amu)'** ***Nucl. Inst. Methods, B17, 1-10 (1986)*** *Comment : S. Ar, Ca (20-80 MeV/amu) -> Be, C, Al, Si, Ti, Ni, Cu, Ag, Ta, Au, Mylar*	**1986-Bimb** 1429
1986	Bussmann, U. Hecking, N. Heidelmann, K. F. TeKaat, E. **'Ranges and Electronic Stopping Powers of 1-24 MeV C and N Ions in Si Targets from Optical Reflectivity Measurements on Bevelled Samples'** ***Nucl. Inst. Methods, B15, 105 (1986)*** *Comment : S,R. C, N (1-24 MeV) -> Si*	**1986-Buss** 1965
1986	Gnaser, H. Bay, H. L. Hofer, W. **'Depth Distributions of Low Energy He Implanted in Solids'** ***Nucl. Inst. Methods, B15, 49-53 (1986)*** *Comment : R, dR. He (0.25-80 keV) -> Si*	**1986-Gnas** 1523

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1986	Guillemaud-Mueller, D. Lampert, M. O. Pons, D. Langevin, M. **'Atomic Number Determination of Energetic Heavy Ions by Energy Loss Measurements using Planar Si Detectors'** ***IEEE Trans. Nucl. Sci., NS-33, 343 (1986)*** *Comment : S,dS. Ar (33 MeV/amu) -> Si. (Si detector response)*	**1986-Guil** 1656
1986	Izsak, K. Berthold, J. Kalbitzer, S. **'Range Phenomena of Low Energy Ions in Solids'** ***Nucl. Inst. Methods, B15, 34-41 (1986)*** *Comment : R. In, Xe, Pb, Cs, Au, (.01 < epsilon < 1) -> Al, Si, Ni, Ri, Ge, Al2O3*	**1986-Izsa** 2198
1986	Wang, K. M. Liu, X. J. Wang, Y. H. **'Range Distributions of 50-400 keV Hg in Amorphous Silicon wand Si-Ar Binary Targets'** ***Nucl. Inst. Methods, B17, 203-206 (1986)*** *Comment : R, dR. Hg (50-400 keV) -> Si, SiAr*	**1986-Wang** 1524
1986	Wilson, R. G. **'Random and Channeled Implantation Profiles and Range Parameters for P and Al in Crystalline and Amorphized Si'** ***J. Appl. Phys., 60 (8), 2797-2805 (1986)*** *Comment : R, dR. P, Al (25-600 keV) -> Si*	**1986-Wils** 1511
1987	Fink, D. Biersack, J. P. Stadele, M. Cheng, V. K. **'Range Profiles of Helium in Solids'** ***Rad. Effects, 104, 1-42 (1987)*** *Comment : R. He-3 (50-1500 keV) -> Be, C, Mg, Al, Si, Ti, V, Mn, Fe, Ca, Ni, Cu, Zn, Ge, Zr, Nb, Mo, Ag, Cd, In, Sn, Sb, Tb, Dy, Er, Ta, W, Ir, Pt, Au, Pb, Bi, SiC, MnO2*	**1987-Fink** 1645
1987	Gauvin, H. Bimbot, R. Herault, J. Anne, R. Bastin, G. **'Stopping Powers of Solids for 16O Ions at Intermediate Energies (20-95 MeV/amu)'** ***Nucl. Inst. Methods, B28, 191-194 (1987)*** *Comment : S. O (20-95 MeV/amu) -> Be, Al, Si, Ti, Ni, Cu, Ag, Ta, Au, Mylar*	**1987-Gauv** 1400
1987	Ingram, D. C. Baker, J. A. Walsh, D. A. Strathman, E. **'Range Distributions of MeV Implants in Silicon - 2'** ***Nucl. Inst. Methods, B21, 460-465 (1987)*** *Comment : R, dR. B, P, Ga (0.4-6.0 MeV) -> Si*	**1987-Ingr** 1514
1987	Kido, Y. **'Energy Straggling for Fast Proton Beams Passing through Solid Materials'** ***Nucl. Inst. Methods, B24/25, 347-352 (1987)*** *Comment : H (300-1000 keV) -> C, Ti, TiC, Si, SiC, SiO2, TiO2*	**1987-Kido** 1664

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1987	Skorupa, W. Wieser, E. Groetzschel, R. Posselt, M. Buecke, H. **'High Energy Implantation and Annealing of Phosphorus in Silicon'** ***Nucl. Inst. Methods, B19/20, 335-339 (1987)*** *Comment : R. P (1 MeV) -> Si*	**1987-Skor** 2015
1987	Weiser, M. Behar, M. Kalbitzer, S. Oberschachtsiek, P. Fink, D. **'A Four-Moments Analysis of H Range Profiles in Silicon'** ***Nucl. Inst. Methods, B29, 587-590 (1987)*** *Comment : R. H (25-300 keV) -> Si*	**1987-Weis** 2197
1988	Behar, M. Weiser, M. Kalbitzer, S. Fink, D. Grande, F. L. **'Implanted Boron Profiles in Silicon'** ***Nucl. Inst. Methods, B34, 316-320 (1988)*** *Comment : R, dR. B (10-1000 keV) -> Si*	**1988-Beha** 1518
1988	Brown, J. G. Galvin, J. E. Yu, K. M. **'High Dose Uranium Ion Implantation into Silicon'** ***Nucl. Inst. Methods, B31, 558-562 (1988)*** *Comment : R, dR. U (157 keV) -> Si (High Dose)*	**1988-Brow** 1532
1988	Grob, J. J. Grob, A. Thevenin, P. Siffert, P. **'Transvers Straggling of MeV Oxygen Ions Implanted in Silicon'** ***Nucl. Inst. Methods, B30, 34-37 (1988)*** *Comment : dR. O (0.6-2 MeV) -> Si*	**1988-Grob** 1512
1988	Herault, J. Bimbot, R. Gauvin, H. Anne, R. Bastin, G. **'Interaction of 20-100 MeV/amu Heavy Ions with Cold Matter'** ***J. Physique Coll., 49C, 7-33 (1988)*** *Comment : S. O, Ar, Ca, Kr, Mo, Xe (24-95 MeV/amu) -> Ne, Ar, Kr, Xe, CH4, C4H10, N, CO2, CF4, Be, Al, Si, Ti, Ni, Cu, Ag, Ta, Au*	**1988-Hera** 1972
1988	Mertens, P. Bauer, P. **'Reference Stopping Cross Sections for 30-600 keV Protons in Silicon'** ***Nucl. Inst. Methods, B33, 133 (1988)*** *Comment : S. H (30-600 keV) -> Si*	**1988-Mert** 1720
1988	Tan, C. Y Xia, Y. Y. Yang, H. Sun, X. F. **'Stopping Powers of 100-600 keV F+, Ar+, As+, Br+, and Xe+ Ions in Silicon'** ***Nucl. Inst. Methods, B33, 142-146 (1988)*** *Comment : S. F, Ar, As, Br, Xe (100-600 keV) -> Si*	**1988-Tan** 1402
1988	Yamaguchi, S. Takahiro, K. Nakajima, H. Fujino, Y. Sagara, S. **'Energy Loss of He Ions in H-Implanted Materials'** ***Nucl. Inst. Methods, B33, 163-167 (1988)*** *Comment : S. He (1.5 MeV) -> Be, Si, Al (doped with H)*	**1988-Yama** 1962

1989
Andersen, H. H.   Hvelplund, P.   Knudsen, H.   Moller, S. P.   Pedersen, J. O. P.
'Measurement of the Z1*3 Contribution to the Stopping Power Using MeV Protons and Antiprotons'
Phys. Rev. Letters, 62, 1731-1734 (1989)
Comment : S. H, H- (0.5-3.0 MeV) -> Si First measurement of anti-proton stopping.
1989-Ande
1598

1989
Behar, M.   Weiser, M.   Kalbitzer, S.   Fink, D.   Grande, P. L.
'High Energy Li Implanted Profiles in Silicon'
Nucl. Inst. Methods, B39, 22-25 (1989)
Comment : R, dR. Li (4.5keV-2 MeV) -> Si
1989-Beha
1516

1989
Grob. J. J.   Grob, A.   Thevenin, P.   Siffert, P.
'A Silicon on Insulator Structure formed by Implantation of MeV Oxygen'
Matl. Sci. Eng., B2, 123-129 (1989)
Comment : R, dR. O (0.6-2.0 MeV) -> Si (High Dose)
1989-Grob
1515

1989
LaFerla, A.   DiFranco, A.   Rimini, E.
'Implants of 15-50 MeV Boron Ions into Silicon'
Matl. Sci. Eng., B2, 69-73 (1989)
Comment : R, dR. B (15-50 MeV) -> Si
1989-LaFe
1522

1989
Weiser, M.   Oberschachtsiek, P.   Gunzler, R.   Schule, V.   Kalbitzer, S.
'Experimental and Calculated Range Moments of Deep Implants'
Mater. Sci. Eng., B2, 55-61 (1989)
Comment : R. H, N, I, Au (.2-5 MeV) -> Si Range distributions/moments.
1989-Weis
2196

1989
Xia, Y.   Tan, C.   Yang, H.   Sun, X.   Liu, J.
'Nucleonic Stopping Powers Derived from Range Measurements for Ions at Low Velocity'
Vacuum, 39, 347-349 (1989)
Comment : S, R. F, Ar, As, Br, Xe -> PbSn, Si
1989-Xia
1939

1990
Bauer, P.
'Stopping Power of Light Ions near the Maximum'
Nucl. Inst. Methods, B45, 673 (1990)
Comment : S. H, H- (30-700 keV) -> C, Al, Si, Ni, Cu, Ag, Au, SiO2, HC2, Al2O3
1990-Baue
1608

1991
Arstila, K.   Keinonen, J.   Tikkanen, P.
'Stopping Power for Low-Velocity Mg Ions in Si, Ge and GaAs'
Phys. Rev. B, 43, 13967-13970 (1991)
Comment : S. Mg (0-0.8 MeV/amu) -> Si, Ge, GaAs
1991-Arst
1910

1991
Bentini, G. G.   Bianconi, M.   Nipoti, R.   Malaguti, F.   Verondini, E.
'Random and Channeling Stopping Power of Nitrogen in Silicon in the 700-1500 keV Range'
Nucl. Inst. Methods, B53, 1-6 (1991)
Comment : S. N(0.7-2.0 MeV) -> Si (random and channeled)
1991-Bent
1917

Citations for Target : **Si**

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1991	Hecking, N. **'Ranges and Electronic Stopping Powers of 1-20 MeV Si Ions in Si Targets as Obtained from Optical Reflectivity Measurements on Bevelled Samples'** ***Nucl. Inst. Methods, B59/60, 619-622 (1991)***	**1991-Heck** 1986
Comment :	*S,R. Si (1-20 MeV0 -> Si*	
1991	Kuronen, A. **'A Study of Stopping Power using Nuclear Methods'** ***Comm. Physico-Math. (Finland), 122, 1-36 (1991)***	**1991-Kuro** 1914
Comment :	*S. Ion [Z=3-22] at (0-0.4 Vo) -> Solids (Z=14-82)*	
1991	Medenwaldt, R. Moller, S. P. Uggerhoj, E. Worn, T. Hvelplund, P. **'Measurement of the Stopping Power of Silicon for Antiprotons between 0.2 - 3 MeV'** ***Nucl. Inst. Methods, B58, 1-5 (1991)***	**1991-Mede** 1716
Comment :	*S. H-(0.2-3 MeV) -> Si Anti-proton stopping powers.*	
1991	Santry, D. C. Werner, R. D. **'Measured Stopping Powers of C-12 and N-14 Ions in Thin Elemental Foils'** ***Nucl. Inst. Methods, B53, 7-14 (1991)***	**1991-Sant** 1916
Comment :	*S. C, N (0.2-2.0 MeV) -> Be, C, Al, Si, Ne, Ag, Au*	
1992	Alexandrov, A. A. Alexandova, I. A. Pyatkov, Y. U. Slyusarenko, A. I. Shemetov, A. N. **'Study of Fission Fragments Channeling in Silicon Monocrystals'** ***Rad. Effects, 124, 191-196 (1992)***	**1992-Alex** 1888
Comment :	*S. U-238 (fission fragments) -> Si*	
1992	Bichsel, H. Hiraoka, T. **'Energy Loss of 70 MeV Protons in Elements'** ***Nucl. Inst. Methods, B66, 345-351 (1992)***	**1992-Bich2** 1624
Comment :	*S. H (70 MeV) -> C, H2O, SiO2, Al, Si, Ti, Cr, Fe, Co, Ni, Cu, Zn, Zr, Nb, Mo, Ag, Cd, In, Sn, Ta, W, Pb*	
1992	Keinonen, J. Arstila, K. Tikkanen, P. **'Electronic Stopping Power of Si and Ge for MeV Energy Si Ions'** ***Appl. Phys. Letters, 60, 228-230 (1992)***	**1992-Kein** 1901
Comment :	*S. Si, P (0-30 MeV) -> Si, Ge*	
1992	Santry, D. C. Werner, R. D. **'Measured Stopping Powers of O-16 and F-19 Ions in Thin Elemental Films'** ***Nucl. Inst. Methods, B69, 167-173 (1992)***	**1992-Sant** 1887
Comment :	*S. O, F (200-2000 keV) -> Be, C, Al, Si, Ni, Ti, Ag, Au*	

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1992	Schule, V. Gunzler, R. Oberschachtsiek, P. Weiser, M. Kalbitzer, S. **'Range Parameters of Deep Ion Implants in Group IV Semiconductors'** ***Nucl. Inst. Methods, B62, 338-345 (1992)*** *Comment : R. Ranges of Heavy Ions (1 MeV/amu) -> C, Si, Ge*	**1992-Schu** 2195
1993	Bentini, G. G. Bianconi, M. Nipoti, R. **'Energy Loss and Equilibrium Charge Distribution of Nitrogen Ions Transmitted through Thin Silicon Crystals'** ***Nucl. Inst. Methods, B80/81, 33-36 (1993)*** *Comment : S. N (1.0-1.8 MeV) -> Si (random, channeled)*	**1993-Bent** 1869
1993	Goppelt, P. Biersack, J. P. Gebauer, B. Fink, D. Bohne, W. **'Range Measurements of Boron Isotopes in Silicon from 600 keV to 2 MeV'** ***Nucl. Inst. Methods, B80/81, 62-64 (1993)*** *Comment : R. B (0.6-2.0 MeV) -> Si*	**1993-Gopp** 2078
1993	Narumi, K. Fujii, Y. Kishine, K. Fujiwara, S. Kimura, K. **'Energy Losses of 12-32 keV H, He and N Ions at Glancing Angle Scattering from Clean Surfaces of Silicon Crystals'** ***J. Phys. Soc. Jap., 62, 1603-1611 (1993)*** *Comment : S. H, He, N (12-32 keV) -> Si Surface scattering effects*	**1993-Naru** 2054
1993	Nieman, D. Oberschachtsiek, P. Kalbitzer, S. Zeindl, H. P. **'Energy Loss and Straggling of MeV He-4 Ions in a Si/Sb Multilayer Target'** ***Nucl. Inst. Methods, B80/81, 37-40 (1993)*** *Comment : S, dS. He (0.1-4.0 MeV) -> Si/Sb Layers*	**1993-Niem** 1868
1993	Tikkanen, P. Keinonen, J. Kangasmaki, A. Fulop, Z. Kiss, A. Z. **'Short Lifetimes in Si-28'** ***Phys. Rev. C, 47, 145-156 (1993)*** *Comment : S. Ta (0-6 V/Vo) -> Si*	**1993-Tikk** 1876
1994	Andersen, J. U. Ball, G. C. Davies, J. A. Davies, W. G. Forster, J. S. **'Energy Loss of Heavy Ions at High Velocity'** ***Phys. Rev., 90, 104 (1994)*** *Comment : S. Br (11-13.5 MeV/amu) -> Si, Ni, Au. Stopping of Br (32+ charge state) with comparison to various theories.*	**1994-Ande** 1995
1994	Avdeichikov, V. V. Bergholt, L. Guttormsen, M. Taylor, J. E. Westerberg, L. **'Light Output and Energy Resolution of CsI, YAG, GSO, BGO, LSO Scintillators for Light Ions'** ***Nucl. Inst. Methods, A349, 216-224 (1994)*** *Comment : S. H, D, He (3-20 MeV/amu)-> CsI, YAG, GSO, BGO, LSO Scintillators*	**1994-Avde** 2074

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1994	Fageeha, O. Howard, J. Block, R. C. **'Distribution of Radial Energy Deposition around the Track of Energetic Charged Particles in Silicon'** ***J. Appl. Phys., 75, 2317-2321 (1994)*** *Comment : S. C, Al, Fe (10-10,000 MeV) -> Si*	**1994-Fage** 2049
1995	Ahlgren, T. Vakevainen, K. Raisanen, J. Rauhala, E. Keinonen, J. **'Range Profiles of 6-10 MeV Nitrogen Ions Implanted in Silicon'** ***Appl., Surf. Sci., 90, 419-423 (1995)*** *Comment : R. N (6-10 MeV) -> Si*	**1995-Ahlg** 2236
1995	Dos Santos, J. H. R. Grande, P. L. Boudinov, H. Behar, M. Stoll, R. **'Electronic Stopping Power of <100> Axial Channelled He Ions in Si Crystals'** ***Nucl. Inst. Methods, B106, 51-54 (1995)*** *Comment : S. He (0.2-4.5 MeV) -> Si*	**1995-Dos** 1832
1995	Kuzmin, L. E. Kazantsev, A. M. **'Heavy Ion Energy Straggling Determination using the BEAM EXPERT Integrated Environment'** ***Bull. Lebedev Phys.(USA), 10, 23-27 (1995)*** *Comment : dS. N (0.6-0.8 MeV) -> Au, Si*	**1995-Kuzm** 2069
1995	Li, Z. Zhou, Z. Y. Zhao, G. Q. Tang, J. Y. Yang, F. **'Measured Stopping Powers for Li Ions in Silicon Single Crystal at 1-5 MeV'** ***Chinese Phys. Letters, 13, 172-174 (1995)*** *Comment : S. Li (1-5 MeV) -> Si*	**1995-Li** 1825
1995	Norlund, K. Keinonen, J. Rauhala, E. Ahlgren, T. **'Range Profiles in Self-Implanted Crystalline Si'** ***Phys. Rev., B52, 15170-15175 (1995)*** *Comment : R. Si (50-100 keV) -> Si*	**1995-Norl** 2235
1995	Petrovic, S. Miletic, L. Neskovic, N. **'Angular Distributions of Ions Transmitted through a very thin Crystal'** ***Nucl. Inst. Methods, B115, 348-354 (1995)*** *Comment : S. C (25 MeV) -> Si (angular and thickness effects)*	**1995-Petr** 2061
1995	Shevchenko, V. A. **'Stopping Power Measurements of Low Energy Protons using Backscattering on the Target'** ***Metall-Novei.-Tekh., 17, 27-29 (1995) Translated in "Physics of Metals"*** *Comment : S. H (80-240 keV) -> Si, Cd, Fe, Au, YBaCuO*	**1995-Shev** 2378
1996	Azuma, T. Komaki, K. Yamazaki, Y. Kakutani, N. Ninomiya, S. **'Charge Exchange and Stopping Power of Channeled Heavy Ions'** ***Nucl. Inst. Methods, B115, 306-309 (1996)*** *Comment : S. C (30 MeV) -> Si (Angular energy loss, and charge states)*	**1996-Azum** 1815

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1996	Gelfort, S. Kerkow, H. Stolle, R. Petukhov, V. P. Romanowski, E. A. **'Angular Dependence of the Electronic Energy Loss for Low Energy Heavy Ions under Channeling Conditions'** ***Nucl. Inst. Methods, B115, 315-318 (1996)***	**1996-Gelf** 1814
Comment :	*S. Channeling of ions He to Kr in Si <110>*	
1996	Goppelt-Langer, P. Yamamoto, S. Aoki, Y. Takeshita, H. Naramoto, H. **'Stopping Powers and Straggling of N-15 Ions for Nuclear Reaction Analysis at 6.385 MeV'** ***Nucl. Inst. Methods, B118, 7-10 (1996)***	**1996-Gopp** 2033
Comment :	*S, dS. N (6.4 MeV) -> H, Si, Nb*	
1996	Ikeda, A. Sumitomo, K. Nishioka, T. Kido, Y. **'Stopping Powers and Energy Straggling for 50-300 keV H in Amorphous Si and Ge Films'** ***Nucl. Inst. Methods, B115, 34-38 (1996)***	**1996-Iked** 2029
Comment :	*S, dS. H (50-300 keV) -> Si, Ge*	
1996	Li, Z. Zhao, G. Q. Zhou, Z. Y. Tang, J. Y. Yang, F. C. **'Measured Stopping Powers of Li Ions in Silicon Single Crystal at 1-5 MeV'** ***Chinese Phys. Letters, 13, 172-174 (1996)***	**1996-Li** 2064
Comment :	*S. Li (1.0 - 5.0 MeV) -> Si (channeling effects)*	
1996	Liu, J. R. Zheng, Z. S. Chu, W. K. **'Stopping Cross Sections of C, Al, Si for Li-7 Ions'** ***Nucl. Inst. Methods, 118, 24-28 (1996)***	**1996-Liu** 0592
Comment :	*S. Li (1-7 MeV) -> C, Al, Si*	
1996	Misdaq, M. A. Elassali, R. **'Average Stopping Powers for Channeled Ions using Calculational and Experimental Methods'** ***Nucl. Inst. Methods, 119, 325-330 (1996)***	**1996-Misd** 0964
Comment :	*S. Light ions -> Si, GaAs (channeled)*	
1996	Niemann, D. Kinac, G. Kalbitzer, S. **'Stopping Power of H, He and N in Si in the Energy Range of 0.02-1.0 MeV/amu'** ***Nucl. Inst. Methods, 118, 11-18 (1996)***	**1996-Niem** 1101
Comment :	*S. H, He, N (.02-1.0 MeV/amu) -> Si*	
1996	Olivera, G. H. Martinez, A. E. Rivarola, R. D. Fainstein, P. D. **'Electronic Stopping Power of Hydrogen Beams Traversing Oxygen'** ***Nucl. Inst. Methods, B111, 7-11 (1996)***	**1996-Oliv** 2031
Comment :	*Theory*	

Citations for Target : **Si**

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1997	Dos Santos, J. H. R. Behar, M. Grande, P. L. Boudinov, H. Kalbitzer, S. **'Electronic Stopping Power of B in Si in Random and <100> Channeling Directions'** ***Phys. Rev., B55, 13651-13657 (1997)*** *Comment : S. B (500 - 9000 keV) -> Si Random and Channeled*	**1997-DosS** 0921
1997	Moller, S. P. Uggerhoj, E. Bluhme, H. Knudsen, H. Mikkelsen, U. **'Direct Measurements of the Stopping Power for Antiprotons of Light and Heavy Targets'** ***Phys. Rev. A, 56, 2930-2939 (1997)*** *Comment : S. H- (50 - 700 keV) -> Al,Si,Ti,Cu,Ag,Ta,Pt,Au*	**1997-Moll** 2364
1997	Moller, S. P. Uggerhoj, E. Bluhme, H. Knudsen, H. Mikkelsen, U. **'Measurement of the Barkas Effect around the Stopping-Power Maximum for Light and Heavy Targets'** ***Nucl. Inst. Methods, B122, 162-166 (1997)*** *Comment : S. H- (50 - 700 keV) -> Si, Au*	**1997-Moll3** 2381
1997	Muller, S. P. Uggerhoj, E. Bluhme, H. Knudsen, H. Mikkelsen, U. **'Measurement of the Barkas Effect Around the Stopping Power Maximum for Light and Heavy Targets'** ***Nucl. Inst. Methods, B122, 162-166 (1997)*** *Comment : S. H- (50-700 keV) -> Si, Au*	**1997-Mull** 2026
1997	Muller, S. P. Uggerhoj, E. Bluhme, H. Knudsen, H. Mikkelsen, U. **'Direct Measurements of the Stopping Power for Anti-Protons on Light and Heavy Targets'** ***Phys. Rev., 56A, 2930-2939 (1997)*** *Comment : S. Anti-protons (H-) -> Al, Si, Ti, Cu, Ag, Ta, Pt, Au*	**1997-Mull2** 2318
1999	Jiang, W. Grotzschel, W. Pilz, W. Schmidt, B Moller, W. **'Random and Channeling Stopping Powers and Charge State Distribtuions in Silicon for 0.2 - 1.2 MeV/u Positive Heavy Ions'** ***Phys. Rev. B, 59, 226-234 (1999)*** *Comment : S. Li, B, C, N, O, P, Cl (0.2 - 1.2 MeV/u) -> Si*	**1999-Jian** 2333
2000	Arstila, K. **'An Experimental Method for Precise Determination of Electronic Stopping Powers for Heavy Ions'** ***Nucl. Inst. Methods, B168, 473-483 (2000)*** *Comment : S. Si -> SiO2, Si, ZrO2, Zr, Al2O3, Al*	**2000-Arst** 3113
2000	Hoshino, Y. Okazawa, T. Nishii, T. Nishimura, T. Kido, Y. **'Correction of Ziegler's Stopping Powers of Al, Si and their Oxides for MeV He Ions'** ***Nucl. Inst. Methods, B171, 409-413 (2000)*** *Comment : S. He (1.1 - 2.6 MeV) -> Al, Si*	**2000-Hosh** 2344

Citations for Target : **Si**

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
2001	DaSilva, D. L. Azevedo, G. de M. Behar, M. Dias, J. F. Grande, P. L. **'Random Energy Loss and Straggling Study of Li into Si'** ***Nucl. Inst. Methods, B175-177, 98-101 (2001)*** *Comment : S. dS. Li (380 - 2500 keV) -> Si*	**2001-daSi** 2348
2001	daSilva, D. L. Azevedo, G. Behar, M. Dias, J. F. Grande, P. L. **'Random Energy Loss and Straggling Study of Li into Si'** ***Nucl. Inst. Methods, B175-177, 98 - 101 (2001)*** *Comment : S, dS. Li -> Si*	**2001-Silv** 3124
2002	Araujo, L.L. Grande, P. L. Behar, M. dos Santos, J. H. R. **'Random Stopping Power and Energy Straggling of 16-O Ions into Amorphous Silicon Target'** ***Nucl. Inst. Methods, B190, 79-83 (2002)*** *Comment : S, dS O -> Si(amor)*	**2002-Arau** 3128
2002	Azevedo, G. Behar, M. Dias, J. F. Grande, P. L. daSilva, D. L. **'Random and Channeling Stopping Powers of He and Li Ions in Si'** ***Phys. Rev., B-65, 075203-1 - 9 (2002)*** *Comment : S. He, Li -> Si*	**2002-Azev** 3122
2002	Barradas, N. P. Jeynes, C. Webb, R. P. Wendler, E. **'Accurate Determination of the Stopping Power of 4-He in Si using Bayesian Inference'** ***Nucl. Inst. Methods, B194, 15-25 (2002)*** *Comment : S. He -> Si*	**2002-Barr** 3108
2002	Fama, M. Lantschner, G. H. Eckardt, J. C. Arista, N. R. Gayone, J. E. **'Energy Loss and Angular Dispersion of 2-200 keV Protons in Amorphous Silicon'** ***Nucl. Inst. Methods, B193, 91-96 (2002)*** *Comment : S. H -> Si(amor)*	**2002-Fama** 3129
2002	Whitlow, H. J. Timmers, H. Elliman, R. G. Weijers, T.D.M. Zhang, Y. **'Measurements of Si Ion Stopping in Amorphous Silicon'** ***Nucl. Inst. Methods, B190, 84-88 (2002)*** *Comment : S, Si -> Si*	**2002-Whit** 3126
2002	Whitlow, H. J. Timmers, H. Elliman, R. G. Weijers, T. D. Zhang, Y. **'Measurement and Uncertianties of Energy Loss in Silicon over a Wide Z1 Range using Time-of-Flight Detector Telescopes'** ***Nucl. Inst. Methods, B195, 133-146 (2002)*** *Comment : S. Li, Be, B, C, N, O, F, Na, Mg, Al, Si, P, Mn, Fe -> Si*	**2002-Whit2** 3136
2004	Araujo, L.L. Mehar, M. Grande, P.L. Dias, J.F. **'Random Energy Loss and Straggling Study of 9-Be Ions in Silicon'** ***Nucl. Inst. Methods, B219-220, 246-250 (2004)*** *Comment : S. dS. Be -> Si*	**2004-Arau** 3131

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
2004	Zhang, Y. Weber, W. J. **'Studies of Electronic Stopping Powers using Time of Flight Spectrometry'** ***Nucl. Inst. Methods, B219-220, 256-262 (2004)*** *Comment : S. He, O, Al -> C, SiC*	**2004-Zha1** 3133
2004	Zhang, Y. Weber, W. Whitlow, H. J. **'Electronic Stopping Powers for Heavy Ions in Silicon'** ***Nucl. Inst. Methods, B215, 48-56 (2004)*** *Comment : S. 14 light ions (Be-Cu) -> Si*	**2004-Zha3** 3138
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